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<p>(21) International Application Number: PCT/US90/05900</p> <p>(22) International Filing Date: 15 October 1990 (15.10.90)</p> <p>(30) Priority data: 423,902 19 October 1989 (19.10.89) US</p> <p>(71) Applicant: THE OHIO STATE UNIVERSITY RESEARCH FOUNDATION [US/US]; 1314 Kinnear Road, Columbus, OH 43212 (US).</p> <p>(72) Inventors: EPSTEIN, Arthur, J. ; 55 Merkle Road, Bexley, OH 43209 (US). YUE, Jiang ; 240 West Eighth Ave., Apt. N, Columbus, OH 43201 (US).</p> <p>(74) Agents: MARTINEAU, Catherine, B. et al.; Emch, Schaffer, Schaub & Porcello Co., P.O. Box 916, Toledo, OH 43692-0916 (US).</p>		<p>(81) Designated States: AT (European patent), AU, BE (European patent), CA, CH (European patent), DE (European patent), DK (European patent), ES (European patent), FR (European patent), GB (European patent), GR (European patent), IT (European patent), JP, KR, LU (European patent), NL (European patent), SE (European patent).</p> <p>Published With international search report. Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</p>
<p>(54) Title: POLYANILINE COMPOSITIONS, PROCESS FOR THEIR PREPARATION AND USES THEREOF</p> <div style="display: flex; justify-content: space-around; align-items: flex-start;"> <div style="text-align: center;"> <p>Structure a Compound I</p> </div> <div style="text-align: center;"> <p>Structure b</p> </div> <div style="text-align: center;"> <p>Structure c</p> </div> <div style="text-align: center;"> <p>Structure d</p> </div> </div> <p>(57) Abstract</p> <p>Self-protonated sulfonic acid substituted polyaniline compositions, processes for their preparation and uses thereof. The sulfonated polyaniline compositions are useful for conduction of electricity, absorption of electromagnetic radiation, modulation of electromagnetic beams and modification of the electromagnetic response of sulfonated polyaniline compositions by chemical or electrochemical means. The sulfonated polyaniline compositions are also useful as a high density erasable data storage medium for use in information storage and process applications. The sulfonated polyaniline compositions provide electronic, chemical, electrochemical and optionally microelectronic devices which use and control the chemical and physical properties of the compositions.</p>		

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POLYANILINE COMPOSITIONS,
PROCESS FOR THEIR PREPARATION AND USES THEREOF

Background of the Invention

The present invention is a continuation-in-part of co-pending application Serial No. 193,964 which was filed on May 13, 1988.

5 The present invention relates to self-protonated sulfonic acid-substituted polyaniline compositions their derivatives, processes for their preparation, and uses thereof.

10 It is desirable in certain applications to have a material whose radiation absorption characteristics and index of refraction can be easily and reversibly modulated. Various polymeric materials have been investigated including polyacetylene, polydiacetylene, polypyrrole, poly (N-methyl-pyrrole), poly(phenylene vinylene), and polythiophene. While these polymeric materials are known to exhibit photoresponsive effects, these materials have deficiencies when considered for certain electromagnetic applications. For example, 15 polyacetylene and polydiacetylene have limited photoresponse, are air sensitive, generally cannot be derivatized, and are not readily soluble and therefore cannot be easily deposited as a thin film from solution. In addition, most materials previously investigated for electromagnetic radiation absorption are not readily tunable, i.e., the photoresponses of the materials cannot be reversibly modulated 20 by an external source of energy.

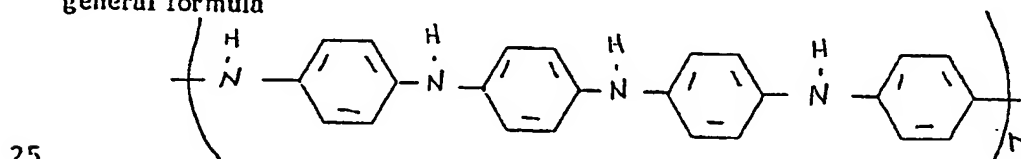
Organic polymers have long been studied for electronic transport and, more recently, for optical properties. The first organic polymers prepared were electrically insulating with conductivities as low as 10^{-14} (ohms cm)⁻¹. The insulating properties are the result of all the electrons in the polymer being

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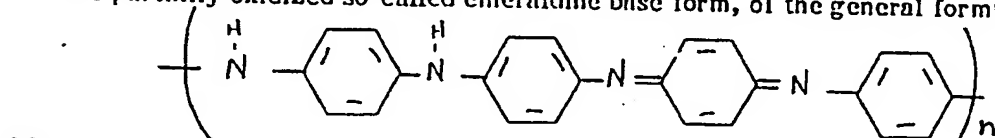
localized in the hybrid-atom molecular orbital bonds, i.e., the saturated carbon framework of the polymer. These insulators, which include polymers such as poly(n-vinylcarbazole) and polyethylene, have extremely large band gaps with energy as high as 5 eV required to excite electrons from the valence to the conduction band. Electrical applications of insulating organic polymers are limited to insulating or supporting materials where low weight and excellent processing and mechanical properties are desirable.

High electrical conductivity has been observed in several conjugated polymer or polyene systems. The first and simplest organic polymer to show high conductivity was "doped" polyacetylene. In the "doped" form its conductivity is in excess of $200 \text{ (ohm cm)}^{-1}$ with new preparations of doped polyacetylene now having conductivities in excess of 10^5 /S cm . Although polyacetylene was first prepared in the late 1950's, it was not until 1977 that this polyene was modified by combining the carbon chain with iodine and other molecular acceptors to produce a material with metallic conductivity.

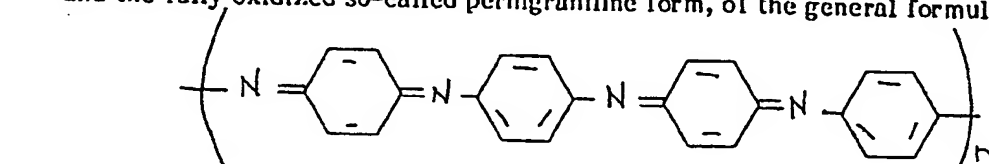
Polyaniline is a family of polymers that has been under intensive study recently because the electronic and optical properties of the polymers can be modified through variations of either the number of protons, the number of electrons, or both. The polyaniline polymer can occur in several general forms including the so-called reduced form (leucoemeraldine base), possessing the general formula



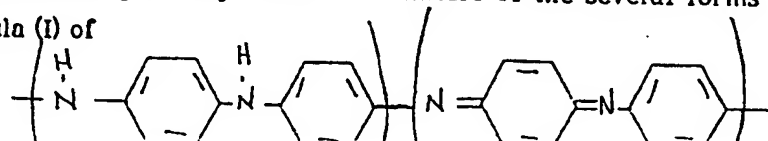
the partially oxidized so-called emeraldine base form, of the general formula



and the fully oxidized so-called pernigraniline form, of the general formula

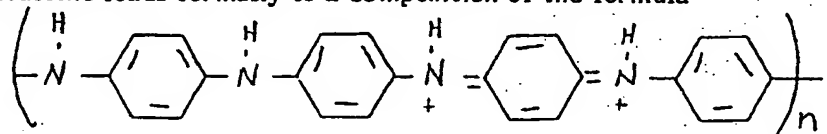


In practice, polyaniline generally exists as a mixture of the several forms with a general formula (I) of

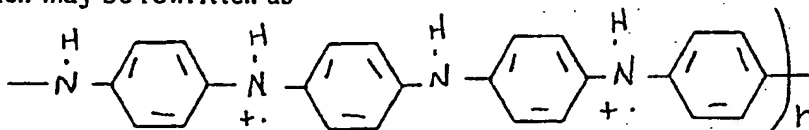


When $0 \leq y \leq 1$, the polyaniline polymers are referred to as poly(paraphenylenecamineimines) in which the oxidation state of the polymer continuously increases with decreasing value of y . The fully reduced poly(paraphenylenecamine) is referred to as leucoemeraldine, having the repeating units indicated above corresponding to a value of $y = 1$. The fully oxidized poly(paraphenylenimine) is referred to as pernigraniline, of repeat unit shown above corresponds to a value of $y = 0$. The partly oxidized poly(paraphenylenimine) with y in the range of greater than or equal to 0.35 and less than or equal to 0.65 is termed emeraldine, though the name emeraldine is often focused on y equal to or approximately 0.5 composition. Thus, the terms "leucoemeraldine", "emeraldine" and "pernigraniline" refer to different oxidation states of polyaniline. Each oxidation state can exist in the form of its base or in its protonated form (salt) by treatment of the base with an acid.

The use of the terms "protonated" and "partially protonated" herein includes, but is not limited to, the addition of hydrogen ions to the polymer by, for example, a protonic acid, such as mineral and/or organic acids. The use of the terms "protonated" and "partially protonated" herein also includes pseudoprotonation, wherein there is introduced into the polymer a cation such as, but not limited to, a metal ion, M^+ . For example, "50%" protonation of emeraldine leads formally to a composition of the formula



which may be rewritten as



Formally, the degree of protonation may vary from a ratio of $[\text{H}^+]/[-\text{N}=] = 0$ to a ratio of $[\text{H}^+]/[-\text{N}=] = 1$. Protonation or partial protonation at the amine ($-\text{NH}-$) sites may also occur.

The electrical and optical properties of the polyaniline polymers vary with the different oxidation states and the different forms. For example, the leucoemeraldine base, emeraldine base and pernigraniline base forms of the polymer are electrically insulating while the emeraldine salt (protonated) form of the polymer is conductive. Protonation of emeraldine base by aqueous HCl (1M HCl) to produce the corresponding salt brings about an increase in electrical conductivity of approximately 10^{12} ; deprotonation occurs reversibly in aqueous

base or upon exposure to vapor of, for example, ammonia. The emeraldine salt form can also be achieved by electrochemical oxidation of the leucoemeraldine base polymer or electrochemical reduction of the pernigraniline base polymer in the presence of an electrolyte of the appropriate pH. The rate of the electrochemical reversibility is very rapid; solid polyaniline can be switched between conducting, protonated and nonconducting states at a rate of approximately 10^5 Hz for electrolytes in solution and even faster with solid electrolytes. (E. Paul, et al., J. Phys. Chem. 1985, 89, 1441-1447). The rate of electrochemical reversibility is also controlled by the thickness of the film, thin films exhibiting a faster rate than thick films. Polyaniline can then be switched from insulating to conducting form as a function of protonation level (controlled by ion insertion) and oxidation state (controlled by electrochemical potential). Thus, in contrast to, for example, the polypyrrole mentioned above, polyaniline can be turned "on" by either a negative or a positive shift of the electrochemical potential, because polyaniline films are essentially insulating at sufficiently negative (approximately 0.00 V vs. SCE) or positive (+0.7 V vs. SCE) electrochemical potentials. Polyaniline can also then be turned "off" by an opposite shift of the electrochemical potential.

The conductivity of polyaniline is known to span 12 orders of magnitude and to be sensitive to pH and other chemical parameters. It is well-known that the resistance of films of both the emeraldine base and 50% protonated emeraldine hydrochloride polymer decrease by a factor of approximately 3 to 4 when exposed to water vapor. The resistance increases only very slowly on removing the water vapor under dynamic vacuum. The polyaniline polymer exhibits conductivities of approximately 1 to 20 Siemens per centimeter (S/cm) when approximately half of its nitrogen atoms are protonated. Electrically conductive polyaniline salts, such as fully protonated emeraldine salt $[(-C_6H_4-NH-C_6H_4-NH^+)-Cl^-]_x$, have high conductivity (10^{-4} to 10^{+2} S/cm) and high dielectric constants (20 to 200) and have a dielectric loss tangent of from below 10^{-3} to approximately 10^1 . Dielectric loss values are obtained in the prior art by, for example, carbon filled polymers, but these losses are not as large nor as readily controlled as those observed for polyaniline.

In addition, polyaniline has been used to coat semiconductor photoelectrodes, to serve as an electrochromatic display material, and to suppress corrosion of iron. Polymers have also recently been under investigation because of the ability to alter their optical properties as the result of exposure to optical excitation.

Polyaniline differs substantially from other polymers such as polyacetylene, polythiophene, polypyrrole and polydiacetylene in several important aspects. First, polyaniline is not charge conjugation symmetric; that is, the Fermi level and band gap are not formed in the center of the pi band, so that the valence and conduction bands are very asymmetric. [S. Stafstrom, J. L. Bredas, A. J. Epstein, H. S. Woo, D. B. Tanner, W. S. Huang, and A. G. MacDiarmid, Phys. Rev. Lett. 59, 1464 (1987)]. Consequently, the energy level positions of doping induced and photoinduced excitations differ from those in charge-conjugation-symmetric polymers such as polyacetylene and polythiophene. Second, both carbon rings and nitrogen atoms are within the conjugation path forming a generalized "A-B" polymer, unlike polypyrrole and polythiophene, whose heteroatoms do not contribute significantly to pi band formation. [M. J. Rice and E. J. Mele, Phys. Rev. Lett. 49, 1455 (1982); J. L. Bredas, B. Themans, J. G. Fripiat, J. M. Andre and R. R. Chance, Phys. Rev. B29, 6761 (1984)]. Third, the emeraldine base form of polyaniline can be converted from an insulating to a metallic state if protons are added to the -N= state sites while the number of electrons on the chain is held constant. [J. C. Chiang and A. G. MacDiarmid, Synth. Met. 13, 193 (1986)]. For example, exposure of emeraldine base to a protonic acid such as HCl causes a transformation to the emeraldine salt form of polyaniline. The emeraldine salt form of polyaniline exhibits metallic properties which are due to the formation of a polaron lattice in the material. [J. M. Ginder, A. F. Richter, A. G. MacDiarmid, and A. J. Epstein, Solid State Commun., 63, 97 (1987); A. J. Epstein, J. M. Funder, F. Zuo, R. W. Bigelow, H. S. Woo, D. B. Tanner, A. F. Richter, W. S. Huang and A. G. MacDiarmid, Synth. Met. 18, 303 (1987); H. Y. Choi, and E. J. Mele, Phys. Rev. Lett. 59, 2188 (1987)].

The present invention is related to the invention disclosed in the co-pending Application Serial No. 305,872, which was filed on February 2, 1989 and is incorporated herein by reference. That application discusses an optical information storage process which provides for erasable high density optical data storage which can be used in information storage and processing applications. The powerful information storage process is based upon the photoexcited optical transformations resulting from the optical absorptions of polyaniline.

While the preparation of polyaniline polymers and the protonated derivatives thereof is known in the art, it is novel herein to prepare sulfonated polyaniline compositions which are capable of being "self-protonated" or "self-doped". The use of the terms "self-protonated" and "self-doped" herein includes,

but is not limited to, the reorganization of hydrogen ions on the polymer i.e., the absence of any counterion not covalently bonded to the polymer chain. For example, self-doping or self-protonation of a polyaniline base polymer leads to a polyaniline salt polymer and a reorganization of the electronic structure which then forms a polaronic metal. The conductivity of such polaronic metal is independent of external protonation.

It is novel herein to use the self-doped sulfonated polyaniline compositions in a wide variety of electrochemical applications such as, for example, electrochromic displays, active electronic switches, in charge storage or battery technologies and in chemical sensors. It is also novel herein to use the self-doped, sulfonated polyaniline in a wide variety of applications for conducting electricity, such as, for example, as discharge layers for electron beam lithography and to form patterned images using electron beam lithography. It is also novel herein to blend self-doped, sulfonated polyaniline with other, insulating, polymers to form conductive thermosets, epoxies, and thermoplastics and for use in the blended or pure form for applications as a medium for electrical discharge.

It is also novel herein to use these self-doped polyaniline compositions for the attenuation of electromagnetic radiation. These self-doped polyaniline polymeric materials can be designed to absorb electromagnetic radiation. In addition, these polymeric materials are useful for developing a method of absorbing the electromagnetic radiation to modulate another electromagnetic beam. These polymeric materials are also useful for developing a method for the modification of the electromagnetic properties of the self-doped polyaniline compositions by chemical or electrochemical means. In addition, the distinct photoinduced properties of the self-doped polyaniline polymers provides a unique opportunity for the application of such polymers to such unique applications as erasable optical information storage technology.

30 Summary of the Invention

The present invention provides a polymeric acid polymer which is capable of protonating or doping itself to form an electrically conducting polymer. The sulfonated polyaniline polymer has faster electronic, electrochemical, chemical, and optical responses and improved solubility than the parent polymer, polyaniline. The solubility of the sulfonated polyaniline polymer is increased greatly due to the presence of the sulfonic group SO_3H . The sulfonated polyaniline polymer is easy to dissolve in basic aqueous solutions in which the

polyaniline polymer is insoluble. In addition, due to the electron withdrawing effects of the SO_3H group, the sulfonated polyaniline polymer has improved environmental stability over the polyaniline polymer. The process for producing the sulfonated polyaniline comprises reacting the polyaniline polymer with concentrated sulfuric acid.

The present invention also relates to the use of sulfonated polyaniline compositions and their derivatives in electronic, electrochemical, chemical, and optical applications. In one aspect of the present invention, the speed of the electrochemical response of the sulfonated polyaniline compositions allows such compositions to be especially useful in such devices as for example, electrochromic displays, active electronic devices such as switches, chemical sensors, and in charge storage or battery applications.

In another aspect of the present invention, the ability of the sulfonated polyaniline compositions to conduct electricity makes such compositions especially useful as, for example, discharge layers for electron beam lithography and use in forming patterned images by electron beam lithography.

The present invention also relates to the use of sulfonated polyaniline as an electrical conductor, either in its pure form or blended with other polymers such as Kevlar or nylon to provide a medium for electrostatic discharge in device housings and also bulk coverings such as carpets and fabrics.

In addition, the invention relates to the use of sulfonated polyaniline or derivatives thereof for such applications as absorbing electromagnetic radiation. The invention further relates to the use of the radiation absorbing sulfonated polyaniline compositions to modulate another electromagnetic beam. The invention also relates to the modification of the electromagnetic response of sulfonated polyaniline compositions by chemical or electrochemical means. The invention further relates to electronic and microelectronic devices based on the chemical and physical properties of the sulfonated polyaniline and its derivatives, and the control of those properties in useful applications. The invention further relates to the use of the sulfonated polyaniline polymer as a high density erasable data storage medium intended for use in information storage and processing applications.

The present invention further relates to the use of sulfonated polyaniline and derivatives thereof for absorbing electromagnetic radiation, including microwaves, radar waves, infrared waves, visible waves, and ultraviolet waves as needed. The invention further relates to the use of the radiation-absorbing sulfonated polyaniline compositions to modulate another electromagnetic beam.

The invention also relates to the modification of the electrical and optical properties of sulfonated polyaniline compositions by chemical or electrochemical means. The invention further relates to electronic and microelectronic devices based on the chemical and physical properties of sulfonated polyaniline and its derivatives.

While the invention relates to both microwave responses and nonlinear optical responses of sulfonic-acid substituted polyaniline and its derivatives, the inventors believe that these phenomena are of different physical origins. The photoresponse is believed to be the result of the reorganization of chemical bonds and to be microscopic. The time frame is believed to be approximately 10^{-13} to 10^{-12} seconds (a rate of 10^{12} to 10^{13} Hz). The use of sulfonated polyaniline compositions to achieve the microwave attenuation of the present invention, however, is believed to be due to a local reorganization of the electronic density on the order of 10^1 to 10^2 Angstroms and on a time frame of approximately 10^{-10} seconds. Both the photoresponse and the microwave attenuation phenomena are believed to be due to the absorption of electromagnetic radiation by the pi electron systems of the sulfonated polyaniline polymer and its derivatives.

The present invention also relates to a method the chemical or electrical erasure of the stored information in bit-wise manner by temporary conversion of a specified bit of a conducting form of a sulfonated polyaniline film. For instance, electrochemical conversion is achieved in a compact solid-state sandwich cell incorporating a solid electrolyte. This electrochemical conversion provides the ability to electrically erase or correct individual bits written optically within the polymer sample.

The present invention also relates to a method for the bit-wise or total erasure of the stored information. For example, application of an intense beam having a wavelength of approximately 1.2 microns such as that available from diode lasers and incandescent sources, to a storage medium composed of a sulfonated polyaniline emeraldine base film will enable the bit-wise erasure of a bit of information written into the medium using approximately 500 nm light. The total erasure of the stored information can be obtained by exposure of the entire storage medium to light of the appropriate wavelength.

Further, the present invention relates to a method for the "layering" of information stored. As the intensity of the photoinduced (write beam produced) change in absorption is proportional to the intensity of the write beam, discrimination of the amount of photoinduced optical absorption by the read

beam enables more than one bit (0,1) to be written at a single bit location. For example, discrimination of two different levels of photoinduced optical absorption squares the total number of bits that may be stored: discrimination of three different photoinduced absorption levels cubes the number of bits that
5 may be stored, etc.

The present invention and the sulfonated polyaniline materials described herein may also be used to provide a medium for recording of hologram as done for example in photorefractive $\text{Bi}_{12}\text{SiO}_{20}$ [J. P. Herriau and J. P. Huignard, Appl. Phys. Lett. 49, 1140 (1986)] and BaTiO_3 [J. Feinberg, Physics Today, 41
10 (10) 46 (1988)]. This technique allows for storage of information in a form of photoinduced fixed gratings within the sulfonated polyaniline material and formation of holographic images.

Brief Description of the Drawings

15 Fig. 1 is a graph illustrating the FTIR spectra of (a) self-doped sulfonated polyaniline; (b) emeraldine base, the parent polymer of sulfonated polyaniline in wave numbers cm^{-1} .

Fig. 2 is a graph illustrating the electronic absorption spectra of (a) ---sulfonated polyaniline film cast from an aqueous NH_4OH solution in a quartz
20 substrate, then dried in air, (peaks at 3.88 and 2.16 eV in 0.1M NH_4OH ; (b) — emeraldine salt film, (peaks at 3.76 and 2.0 eV) in NMP.

Fig. 3 is a graph illustrating the cyclic voltammograms (50mV/s) of (a) —sulfonated polyaniline in 1M HCl, (b) ---polyaniline in 1M HCl.

25 Fig. 4 is a graph illustrating the anodic peak current vs sweep rate of cyclic voltammograms in aqueous 1.0M HCl electrolyte at 298K.

Fig. 5 is a graph illustrating the relationship between $E_{1/2}$ (50mV/s) and pH (a)ooooo the first, (2) ●●●●●● the second redox process of sulfonated polyaniline in the pH range -0.2 to 7.

30 Fig. 6 is a schematic illustration of the equilibria among different structures of self-doped sulfonated polyaniline.

Fig. 7 is a schematic illustration of the equilibrium between self-doped sulfonated polyaniline and its base form in aqueous NH_4OH solution.

Fig. 8 is a schematic illustration of the redox process of the sulfonated polyaniline during sweeping the potential from -0.2 ~ 1.0 v vs Ag/AgCl.

35 Figs. 9-15 are schematic illustrations of alternative embodiments of the invention utilizing the optical properties.

Figs. 16-19 are schematic illustrations of waveguides utilizing the microwave absorption properties of the invention for absorbing microwaves propagated through the waveguide.

Fig. 20 is a schematic illustration of an alternative embodiment in which a surface is coated with a material embodying the present invention for preventing microwave reflections from the coated material.

Figs. 21 and 22 are schematic illustrations of alternative embodiments in which a microwave strip conductor is coated with material embodying the present invention.

Figs. 23 and 24 are schematic illustrations of microwave strip embodiments including an electrolyte for the controlled variation of the microwave absorption properties along the propagation axis of the microwave strip conductors.

Figs. 25 and 26 illustrate embodiments utilizing thermally responsive films which have materials embodying the present invention distributed within the film.

Fig. 27 is a schematic illustration of a configuration for use in the present invention for electrochemical bit-wise write or erasure of stored information.

Fig. 28 is a top view of the schematic illustration of Fig. 26.

Fig. 29 is a side view of a schematic illustration of a sulfonated polyaniline containing optical disk device incorporating a rotating optical disk, laser and mirror for writing bits of information, and laser and mirror for reading the photoinduced information.

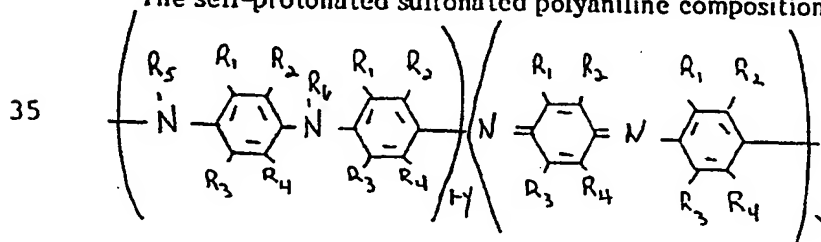
Fig. 30 is a schematic illustration of the use of sulfonated polyaniline film in holographic and photoinduced grating applications.

Fig. 31 is a schematic illustration of the use of a thick sample of sulfonated polyaniline or sulfonated polyaniline dispersed in a transparent host polymer in three-dimensional holographic and photoinduced grating applications.

Detailed Description of the Invention

The present invention relates to sulfonic acid substituted polyaniline compositions, their derivatives, processes for their preparation and uses thereof.

The self-protonated sulfonated polyaniline compositions have the formula I:



wherein $0 \leq y \leq 1$; R_1, R_2, R_3, R_4, R_5 and R_6 are independently selected from the group consisting of H, $-\text{SO}_3^-$, $-\text{SO}_3\text{H}$, $-\text{R}_7\text{SO}_3^-$, $-\text{R}_7\text{SO}_3\text{H}$, $-\text{OCH}_3$, $-\text{CH}_3$, $-\text{C}_2\text{H}_5$, $-\text{F}$, $-\text{Cl}$, $-\text{Br}$, $-\text{I}$, $-\text{NR}_7$, $-\text{NHCOR}_7$, $-\text{OH}$, $-\text{O}^-$, $-\text{SR}_7$, $-\text{OR}_7$, $-\text{OCOR}_7$, $-\text{NO}_2$, $-\text{COOH}$, $-\text{COOR}_7$, $-\text{COR}_7$, $-\text{CHO}$ and $-\text{CN}$, wherein R_7 is a C_1 - C_8 alkyl, aryl or aralkyl group. For the sake of clarity, the structure shown in formula I is in the non self-protonated form.

The fraction of rings containing at least one R_1, R_2, R_3 or R_4 groups being an $-\text{SO}_3^-$, $-\text{SO}_3\text{H}$, $-\text{R}_7\text{SO}_3^-$ or $-\text{R}_7\text{SO}_3\text{H}$ can be varied from a few percent to one hundred percent. In certain embodiments the percentage ranges from at least approximately 20% up to and including 100%. It is within the contemplated scope of the present invention that the $-\text{R}_7\text{SO}_3^-$ and $-\text{R}_7\text{SO}_3\text{H}$ substituents can be varied so that the sulfonated polyaniline is soluble in a range of solvents in order to make the sulfonated polyaniline polymer more easily blendable with other polymers and/or more easily cast onto a variety of surfaces.

The solubility of sulfonated polyaniline can be varied by changing the degree of sulfonation (i.e., the sulfonation time and/or temperature in $\text{H}_2\text{SO}_4(\text{SO}_3)$). It is noted that the oxidation state of the polymer (from leucoemeraldine through emeraldine to pernigraniline) and the degree of sulfonation (x) can be independently varied. Here x is the fraction of C_6 rings which have an SO_3^- or SO_3H group attached.

When $x=0$, the polymer does not dissolve in either basic or acidic aqueous solutions. Upon increasing the value of x , the polymer becomes soluble in strongly basic, basic, weakly basic and eventually in acidic aqueous solutions. This progressive improvement in solubility implies that the polymer becomes soluble in neutral media, particularly H_2O , at the appropriate value of x , yielding a water-soluble conducting polymer. The color of soluble sulfonated polyaniline in acidic solution is green, indicating it is the conducting salt form.

The solubility of polyaniline is increased greatly in basic aqueous solution by the presence of $-\text{SO}_3\text{H}$ group on the phenyl rings. This is in contrast with polyaniline which when washed with basic solutions, converts to the insoluble base form.

Protonation of the emeraldine base polymer leads to the emeraldine salt polymer and a reorganization of the electronic structure to form a polaronic metal. Since benzenesulfonic acid is a strong acid, about as strong as hydrochloric acid, the sulfonated polyaniline is capable of self-doping. Hence, the conductivity of the sulfonated polyaniline is independent of external protonation.

Being able to dope itself, the sulfonated polyaniline polymer has enhanced optical and electrical response to electrochemical potential as compared with the parent polyaniline polymer. Since the solid-state diffusion of counterions in and out of a polymer during electrochemical processes is often the rate
5 controlling step in the kinetics, it also limits the speed of both optical and electrical response of polymers. In the self-doped conjugated polymer of the present invention, the counterions are not necessary from the medium. The positive charge introduced into the conjugated pi electron system of the backbone of the polymer is compensated by the protons migrating out of the
10 polymer, or vice versa, leaving behind the opposite charged counterion. Being the smallest and most mobile ion, proton hopping mechanisms lead to relatively fast doping kinetics as compared to those counterions migrating in or out of the polymer. As a consequence, it is possible to achieve sufficient speed to be useful for a variety of technological applications.

15 The sulfonated polyaniline polymers of the present invention provide opportunities to use the phenomena of the dependence of electrical and optical properties on the backbone chain conformation and on the substituent as well as chain properties which change the chemical properties of polyaniline in a number of useful applications. The side groups on polyaniline also can affect the charge
20 transport in polyaniline. Theoretical studies of polyaniline indicate that the bandgap and bandwidth are affected by the torsion angle (dihedral angle) between adjacent rings on the polymer chain. The torsion angle influences the electronic properties of many conducting polymers with aromatic backbones. For example, poly(o-toluidine) has been studied and the results show that the
25 reduction in pi conjugation of the alkyl derivatives of polyaniline is caused primarily by steric effect.

The present invention discloses herein the synthesis, the electronic, electrochemical and optical properties of sulfonated polyaniline. It is disclosed herein that without external doping, the sulfonated polyaniline has a conductivity
30 of 0.5 S/cm, which makes the sulfonated polyaniline a self-doped conducting polymer. The results indicate that the amount of charge injected into or ejected out of the sulfonated polyaniline polymer is quite similar to that of polyaniline. Charge transfer doping within a specific potential range in solutions such as 1.0 M HCl and 0.5M H₂SO₄ is highly reversible in the air reflecting the
35 environmental stability introduced by the sulfonic acid groups. The inventors present the dependence of positions of redox peaks on different pH values and compare the results with those of sulfonated polyaniline. In contrast with

polyaniline, the first redox process depends on pH in the value range of $-0.2 \sim 7$ due to the sulfonic acid protons on the sulfonated polyaniline backbones. The second redox process depends on the pH in a manner similar to that of polyaniline.

5 The chemical synthesis of the sulfonated polyaniline polymers of the present invention is accomplished by reacting polyaniline with concentrated or fuming sulfuric acid. Various methods for such synthesis are disclosed below.

Materials - Aniline and other chemicals were obtained from Aldrich and were all reagent grade or better. Hydrochloric acid and ammonium hydroxide
10 were used as received. Different pH buffer solutions were commercially purchased.

Chemical Synthesis I: Emeraldine hydrochloride powder was synthesized from aniline and $(\text{NH}_4)_2\text{S}_2\text{O}_8$ then converted to analytically pure emeraldine base polyaniline using the method described previously in A. G. MacDiarmid, J. C.
15 Chiang, A. F. Richter, N. L. D. Somasiri and A. J. Epstein in L. Alcacer (ed.) Conducting Polymers, D. Reidel Publishing Co., Dordrecht, The Netherlands (1987).

For the sulfonation of polyaniline, 1.5g polyaniline (dry emeraldine base form) was dissolved into 40ml fuming sulfuric acid $\text{H}_2\text{SO}_4(\text{SO}_3)$ with constant
20 stirring at room temperature. During the sulfonation period the color of the solution changed from dark purple to dark blue. After approximately 2 hours, the solution was slowly added during about 20 minutes to 200ml methanol while maintaining the temperature between about $10-20^\circ\text{C}$ by an ice bath. A green powder precipitate was formed during the mixing. After the mixing, 100ml less
25 polar acetone was added to the solution in order to increase the precipitate. The green powder was then collected on a Buchner funnel using a water aspirator. The precipitate cake was washed portionwise (50ml/portion) with methanol until the portion of the filtrate showed $\text{pH}=7$ when tested by wet pH paper. The liquid
30 level in the Buchner funnel was constantly adjusted so that it remained above the top of the precipitate. This prevented cracking of the precipitate cake, which would result in inefficient washing of the precipitate cake.

After the above washing, the precipitate remained under suction for approximately 10 minutes. It was then transferred on the filter paper to a vacuum desiccator and dried under dynamic vacuum for 24 hours. Elemental
35 analyses, as shown in Table I are consistent with the composition shown in Fig. 6 as structure a, compound I, which is sulfonated, protonated polyaniline in the emeraldine oxidative state. The self-doped polyaniline is readily dissolved in a

dilute aqueous base solution to form a homogeneous blue-violet solution. The solubility of compound I in 0.1M NH_4OH and NaOH is $\sim 23\text{mg/ml}$.

Chemical Synthesis II: 1.5g polyaniline (dry emeraldine base form) was dissolved into 40ml concentrated sulfuric acid H_2SO_4 , and the temperature slowly raised from the room temperature to 70°C in water bath in 3 hour period with the constant stirring. The temperature was kept at 70°C for 15 hours. Then the temperature was raised to 95°C within 0.5 hour and kept there for 4 hours. The reaction mixture was cooled down to room temperature. The product was very slowly added to -38°C ice made from 160ml distilled H_2O in order to precipitate the polymer. The temperature of the solution was not allowed to reach higher than 0°C during the process. After the temperature of the solution reached room temperature the solution was filtered to obtain a fine powder of sulfonated polyaniline. Large particles were obtained by subsequently heating the room temperature solution up to 70°C in a two hour period, then cooling to room temperature, and conducting filtration to separate the sulfonated polyaniline from the solution. The sulfonated polyaniline was washed with an excess of H_2O until the filtrate was neutral (as tested by pH paper). Dry sulfonated polyaniline was obtained by pumping under dynamic vacuum at room temperature for 48 hours.

Chemical Synthesis III: From the Chemical Synthesis II described above a copolymer (i.e., the polymer mixture of polyanilines and sulfonated polyaniline) was obtained by partially sulfonating polyaniline. This was done in exactly the same way described in the Chemical Synthesis II except utilizing shorter sulfonation times and/or lower sulfonation temperature.

Chemical Synthesis IV: Another way to prepare the copolymer polyaniline-sulfonated polyaniline was to react 2-aminobenzene-sulfonic acid (2ASA) with oxidizing agent in the presence of aniline. 10g (0.58mol) 2ASA and 2ml (0.02mol) aniline were dissolved in 500ml 1M HCl . A prepared solution of 6.609g (0.029mol) $(\text{NH}_4)_2\text{S}_2\text{O}_8$ in 200ml 1M HCl was added dropwise to the monomer solution with vigorous stirring during a period of 10 minutes. After 1.5 hours, the precipitate was collected on a Buchner funnel. The precipitate was washed with 1M HCl until the filtrate was colorless. Then the precipitate was washed by 500ml H_2O . To ensure that the copolymer was in its neutral form, the precipitate was then transferred into a beaker containing 500ml of H_2O and stirred at room temperature for 4 hours. The mixture was filtered until the pH of the filtrate was 7. The dry copolymer was obtained by pumping under dynamic vacuum at room temperature for 48 hours.

- 15 -

Infrared and electronic spectra. Infrared spectra were obtained by mixing the compound I into KBr matrix, pressing into pellets and recording on an FTIR spectrometer.

5 For taking electronic spectra the compound I was dissolved in 0.1M NH_4OH to form a homogeneous solution, the polymer solution was then cast on a quartz substrate. Slow evaporation of the aqueous solution of the compound II (ammonium salt) in air at room temperature resulted in spontaneous removal of the weak volatile base, NH_3 with reformation of the compound I.

10 Electron spin resonance. Temperature dependent (30K to 295K) electron spin resonance was measured for the compound I using a Bruker 300 spectrometer and an Oxford 900 temperature control system.

Conductivity measurement. Conductivities of the compound I was measured on compressed pellets of the powder by using four point probe
15 techniques with a Keithley 220 constant current source and Keithley 181 voltmeter.

Cyclic voltammetry studies. Cyclic voltammetry studies were carried out using a Hokto Corporation (HC) Model HA-301 potentiostat/galvanostat with HC HC-201 digital coulometer. The IIC IIB-111 universal programmer was used for
20 the generation of the sweep signals which were fed into the HA-301. Voltammograms were recorded on a Hewlett-Packard Model 7046B 'XYY' recorder with an optional time base function. For the studies of current peak changing with the sweep rate, a Nicolet Model 370 digital oscilloscope with digitizer and disk-drive plug-in was used for recording i_p in the high frequency
25 characterization experiments. A standard three electrode system was enclosed in a dual compartment cell with a fine porosity glass frit separating the working electrode and reference electrode from the counter electrode. Platinum disks (1.0cm^2) were used as working and counter electrodes. A Ag/AgCl, saturated KCl electrode encased with a luggin probe was used as a reference electrode.
30 1.0M HCl(20ml) was used as the electrolyte. All studies, except scan rate dependence of current peak, were performed at a sweep rate of 50mV/s. Since preliminary observations indicated that air did not have any effect on the cyclic voltammograms, all operations were carried out in the presence of air.

The compound I was cast on a Pt electrode by evaporating a solution of the
35 polymer in 0.1M ammonium hydroxide and subsequently dried in air. In order to obtain reproducible cyclic voltammograms the electrode was preconditioned by cycling between -0.2 and 0.4 volts vs Ag/AgCl for ~ 10 minutes (25 cycles).

Structure Characterization and Physical Properties. Elemental analyses, infrared and electronic spectroscopy, conductivity and cyclic voltammetry studies are consistent with the sulfonation of emeraldine base with fuming sulfuric acid proceeding to give a self-doped, sulfonated, protonated forms of the emeraldine oxidative state of polyaniline, the compound I which has a conductivity of ~ 0.5 S/cm. This polymer can be regarded as being formed by the hypothetically initial formation of the strong acid, shown as structure b in Fig. 6, which then immediately protonates the imine nitrogen atoms to give the conducting polymer in an entirely analogous manner to strong acids such as HCl. Treatment of the structure b compound with an aqueous (ammonium) base yields the sulfonated, non-protonated insulating ammonium salt forms analogous to emeraldine base, viz, the structure c compound shown in Fig 6.

With respect to the above structure, sulfonation occurs preferentially in alternating rings and that under the present experimental conditions, only half the rings were sulfonated. This is consistent with the increased stability of the semiquinone form. Further sulfonation and consequently double protonation of nitrogen atoms convert some of the $-(NH)-$ to $-(NH_2^+)-$ and hence reduce the conjugation of the polymer. The FTIR spectrum shown in Fig. 1 of the self-doped polyaniline, the compound I, is consistent with the presence of $-SO_3^-$ groups alternated to the aromatic rings. IR shows absorption maxima of out of plane bending of aromatic hydrogens at 820 and 870cm^{-1} are indicative of 1, 2, 4 trisubstituteds on the rings. The absorptions are not present in the 1, 2 disubstituted emeraldine base from which the compound I was synthesized. Absorption peaks at 1080 , 700 and 590cm^{-1} are consistent with the presence of SO_3^- groups.

The conductivity of the compound I ($\sigma \sim 0.5$ S/cm) is similar to that of emeraldine hydrochloride measured under the same experimental conditions ($\sigma \sim 1-5$ S/cm; laboratory air), but lower than that $\sigma \sim 18$ S/cm of high molecular weight emeraldine hydrochloride. The self-doped sulfonated polyaniline with emeraldine oxidative state differs dramatically from nonexternally doped polyaniline in conductivity. Since sulfonic acid is a strong acid, approximately as strong as hydrochloric acid, the compound I is capable of doping itself. Pressed pellets of the dark green self-doped compound I had a room temperature conductivity of ~ 0.5 S/cm in contrast to the purple color and insulating behavior of polyaniline emeraldine base form. However, the conductivity of compound I is lower than that of emeraldine hydrochloride pressed pellets; analogy with earlier

study of poly(o-toluidine), the lower conductivity is in accord with increased conduction electron localization induced by the side chain effects of $-\text{SO}_3^-$.

The solubility of the compound I also differs markedly from that of the corresponding polyaniline polymer. The compound I dissolves completely in aqueous 0.1M NH_4OH or NaOH to give a blue-violet solution while polyaniline washed with such solvent converts to the insoluble base form. The compound I partially dissolves in NMP to form a blue color solution and as well as DMSO (dimethyl sulfoxide) to show green color. Treatment of the self-doped polyaniline, compound I, with an aqueous base proceeds consequently to the deprotonation of the backbone of the polymer to form the structure corresponding to emeraldine base, as shown in the reaction A or reaction B depicted in Fig. 7.

The deprotonation results in a 9 or 10 order of magnitude decrease in conductivity. Compound I differs from emeraldine hydrochloride in that it is soluble in aqueous 0.1M NH_4OH and NaOH .

Based on solid state ^{13}C NMR studies, [T. Hjertberg, W.R. Salaneck, I. Landstrom, N.L. D. Somasiri and A.G. MacDiarmid, J. Blymer Sci; Polym. Lett. Ed., 23 (1985) 503] it has been reported that adjacent phenyl rings of the emeraldine backbone are noncoplanar. Introduction of sulfonic acid groups on phenyl rings of the polyaniline backbone can be expected to increase the torsional angle between adjacent rings to relieve steric strain.

Comparisons of the electronic absorption spectra of the compound I and emeraldine base provide insight into changes in the molecular geometry caused by the sulfonic group-substitution on the polyaniline backbone. Steric effects are considered in the interpretation of the electronic absorption spectra of the sulfonated polyaniline. In order to compare the feature of the electronic spectra of the self-doped polymer (compound I) and emeraldine hydrochloride, their spectra are given in Fig. 2. The high energy absorption band at 320nm(3.88eV) and 326nm(3.81eV) for compound I and emeraldine hydrochloride, respectively, is assigned to the π - π^* transition based on earlier experimental and theoretical studies. The other two absorption bands at 435nm(2.38eV) and 850nm(1.46eV) for the compound I, 413nm(3.00eV) and 826nm(1.50eV) for emeraldine hydrochloride, have been assigned to the optical absorption of the metallic polaron band of the salt form. The hypsochromic shift of the π - π^* transition in going from emeraldine hydrochloride to compound I is again in accord with decreased extent of conjugation caused by increased phenyl ring torsion angle which results from steric repulsion between the $-\text{SO}_3^-$ groups and hydrogens on the adjacent phenyl

rings. The bathochromic shift of the polaron band transition is also in agreement with relative energy band shifts expected for increased ring torsion angles.

Temperature dependent electron spin resonance studies show a $\sim 0.4G$ peak to peak linewidth for compound I at room temperature similar in intensity to that of emeraldine salt. This result support that compound I is in the polysemiquinone (polaron energy band) state.

Redox Properties: The color of a sulfonated polyaniline film on Pt electrode in 1M HCl electrolyte was changed by varying the applied potential. These color changes were similar to those of polyaniline under the same conditions. When the potential was scanned between -0.2 to $0.5V$ vs Ag/AgCl a pair of redox peaks were found for sulfonated polyaniline electrode as seen in Fig. 3. The polymer was initially transparent yellow at $-0.2V$ (reduced state) and changed to a green color at $0.5V$. The earlier studies of polyaniline showed that repeated potential cycling between -0.2 and $0.5V$ vs SCE in 1M ZnCl₂ + 0.5M (NH₄)₂Cl could be performed without causing degradation of the polymer. In a potential scan range between -0.2 and $0.6V$ vs SCE in 1M HCl polyaniline film is fairly stable and the shape of the voltammograms changed little during 5×10^3 cycles. A similar stability was observed for sulfonated polyaniline, the voltammograms of film in 1M HCl remained almost the same after 48 hr. scan in the range of -0.2 and $0.6V$ with the scan rate 50 mV/s (approximately 5,000 cycles). The typical cyclic voltammograms of sulfonated polyaniline polymer films in 1M HCl exhibited a sharp anodic peak at $0.35V$ with $\Delta E_{p/2}$ approximately $0.10V$ and a broad cathodic peak at $0.24V$ with $\Delta E_{p/2} \sim 0.14V$.

The higher oxidative potential of the first anodic peak of sulfonated polyaniline as compared with that of polyaniline is expected due to the steric and electronic effects of $-SO_3H$ function group in 1M HCl. Steric effect of short range forces from ortho substituting $-SO_3H$ changes the basicity of the amino group. These forces may be steric compression exerted in different degrees in the emeraldine forms of the polymer backbone and a pressure-produced twisting of the amine or imine groups with a consequent (partial) breakdown of the conjugation, and therefore a modification of the mesomeric effect on basic strength of amine or imine groups.

Introduction of a $-SO_3H$ group on phenyl rings and consequent increase in the torsion angle will decrease the degree of orbital overlap between the phenyl pi-electrons and the nitrogen lone pairs. This decreases the extent of pi-conjugation and raises the energy of the half-oxidized semiquinone cation radicals. This lower thermodynamic stability of the half-oxidized semiquinone

results in difficulty for fully reduced polymer to be oxidized at the first anodic process. As a consequence, this increases the oxidation potential of the polyamine form of the sulfonated polyaniline. In addition, Flurschein first pointed out that all ortho-substituents reduce the basic strength of the primary
5 aniline bases. This also can be expected for the sulfonated polyaniline reduced leucoemeraldine form. At the first anodic peak, the leucoemeraldine base form of sulfonated polyaniline is transformed to the ionic self-doped emeraldine salt form. The acidic center of the emeraldine salt form of sulfonated polyaniline, being strongly solvated, would likely have a larger effective volume than the
10 groups in the neutral base. As a consequence of this there is an increased steric compression that should increase the relative thermodynamic stability of the base. That is, it should make the base weaker, or its conjugate acid stronger. In other words, higher oxidative potential than polyaniline. Because of poor conjugation of $-SO_3H$ with nitrogen lone pair electrons during the first oxidizing
15 process, the steric effect is a dominant factor.

The situation is different at the second anodic process which had an anodic peak at 0.76V in 1M HCl. During this oxidation process the half-oxidized semiquinone cation radicals are further oxidized into the (nonprotonated) quinonediimine (pernigraniline form) which may be facilitated by the formation
20 of two, sp^2 -hybridized nitrogen. Some of the steric strain may be relieved by the wider C-N=C bond angles at the quinoid groups than the benzenoid ones. However, the better conjugation of lone pairs at nitrogen atoms with pi-electrons on phenyl rings as well as the electron withdrawing property of $-SO_3H$ lowers the electron density on the nitrogen atoms. These effects raise the
25 energy of forming fully-oxidized semiquinone dication radicals. The oxidative potential for the second redox process is similar to that of the parent polyaniline. In the second anodic process, the electron-withdrawing property of $-SO_3H$ is more important than the steric effect since the poly(o-toluidine) has similar steric repulsions yet lower oxidative potential due to the electron-
30 donating property of methyl group.

When sulfonated polyaniline film was scanned between a potential -0.2 to 0.9V in 1M HCl, as seen in Fig. 3, two distinct pairs of redox peaks are found. The second anodic peak is at 0.75V for sulfonated polyaniline, which is similar to
35 that of parent polyaniline (0.75V vs Ag/AgCl). The implication is that the leucoemeraldine form of sulfonated polyaniline is more oxidatively stable than its parent polyaniline. The cyclic voltammogram behavior of sulfonated polyaniline in 1M HCl electrolyte showed good stability in air. However, once

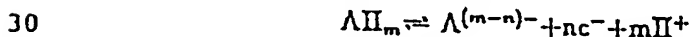
- 20 -

the potential was higher than 0.8V a third anodic peak appeared between two previous peaks. This is due to the degradation of the sulfonated polyaniline polymer. In the high potential region the polymer degraded in the aqueous solution of HCl forming p-benzoquinone or hydroquinone by hydrolysis of overoxidized polymers. The rate of degradation was strongly dependent on the applied potentials.

The scan rate dependence of the current peak of polymer film indicates that the electron transfer through the film is fast. The first anodic peak current shown in Fig. 3 exhibits a linear relationship with a scan rate v . The relationship is linear between i_p and v at least up to a scan rate of 2000mV/s, as seen in Fig. 4, as expected for the reaction of surface localized materials. These redox reactions are faster than polyaniline due to the sulfonic group on phenyl rings. For polyaniline there are no counterions in the backbone of neutral polymer. During electrochemically cycling between two different oxidation states (i.e., doping and dedoping), the counterions must migrate into the polymer during doping process and diffuse out of polymer in dedoping process in order to compensate the charge. This solid-state diffusion process is often the rate limiting step in the kinetics. However, because of $-SO_3H$ group in the backbones of the sulfonated polyaniline polymer, when positive charge is introduced into the pi-electron system (doping or oxidizing), the system can be compensated by proton migrating out of the polymer from the $-SO_3H$ group leaving the negative charged counterions behind the backbones of the polymer. This is illustrated in the scheme as shown in Fig. 8, (1), (2).

From (1) to (2) H^+ migrated out of polymer instead of Cl^- diffused into the polymer. Since the proton is the smallest ion with the highest mobility, the sulfonated polyaniline is expected to have a faster kinetic process than that of polyaniline.

Dependence of Peak Positions on pH: For the reversible redox reaction,



The corresponding Nernst equation is:

$$\begin{aligned} E_{red} &= E_{red}^0 + \frac{RT}{nF} \ln \frac{[A^{(m-n)-}][H^+]^m}{[A\Pi_m]} \\ &= E_{red}^0 + \frac{0.059}{n} \log \frac{[A^{(m-n)-}]}{[A\Pi_m]} + 0.059 \frac{m}{n} \log [H^+] \\ &= E_{red}^0 + 0.059 \frac{m}{n} \log [H^+] \end{aligned}$$

at 25°C.

It clearly shows that in a reaction in which the proton is involved the reduction potential is dependent on pH. If the pH is changed in a system with a given fixed ratio of $A^{(m-n)-}$ and AH_m , then a plot of $E_{1/2}$ vs pH will give a straight line with the slope $-0.059m/n$ V, or $-59m/n$ mV per pH unit. If the numbers of protons and electrons involved in this redox reaction are equal, say $AH = A + H^+ + e^-$, the slope of the line will be -59 mV per pH unit. However, if the process is as $AH_2^+ = A + 2H^+ + e^-$, where the number of protons liberated is twice the number of electrons involved, an analogous plot would have a slope of $59 \times 2/1 = 118$ (mV) per pH unit.

Fig. 5 shows the potential dependence of the first and second redox processes of sulfonated polyaniline on pH (pH range from -0.2 to 5). In contrast with polyaniline, in which the first redox process is independent on the pH in such range (though it is dependent on pH at lower pH levels), the potential of the first redox process of sulfonated polyaniline was linearly changed with the pH values with the slope of -59 mV/pH due to the active protons in $-SO_3H$ function group. This is consistent with the redox scheme shown in Fig. 8, (1), (2).

At the second redox process, however, the position of the $E_{1/2}$ changed linearly with pH with the slope of 120 mV/pH, twice as large as the first one with respect to the pH values. This suggests the redox process as (3) \sim (5) shown in Fig. 8 with an electronic state at 0.76 V similar to that of the pernigraniline form for polyaniline.

Compared with polyaniline, the second redox process of sulfonated polyaniline has a similar pH dependence as polyaniline due to the same backbone structure, however, its first redox process behaves differently from polyaniline in pH range -0.2 to 7 because of active protons on the polyaniline backbone.

The present invention thus discloses that sulfonated polyaniline can be synthesized chemically. Elemental analyses and FTIR data suggest that, depending on the sulfonation times and temperatures, the number of $-SO_3H$ groups per phenyl ring varied from 0.2 to 1.0 . The conductivity is independent of pH in the range of pH values smaller than or equal to 7 . The cyclic voltammograms of sulfonated polyaniline consist of two pairs of well resolved redox peaks corresponding to the conversion of amine nitrogen to semiquinone (polaron) and of the polaron to bipolaron (or imine nitrogen), respectively. Two effects, steric and electronic, are associated with the sulfonic substituent. The steric effect is largely responsible for: (1) the decrease in the conductivity; (2) the hypsochromic shifts of the $\pi - \pi^*$ transition band in UV-region; and (3) the

increase in the thermodynamic stability of the amine nitrogen base as compared with the parent polyaniline. The electronic effect is mainly responsible for: (1) independence of the conductivity on the pH; (2) dependence of the first redox process on pH; and (3) the decrease in the basicity of the imine species of the sulfonated polyaniline.

The present invention further relates to the uses of the sulfonated polyaniline compositions and their derivatives in electronic, electrochemical, chemical, and optical applications. The sulfonated polyaniline compositions have a more rapid electrochemical response than polyaniline. The ability of the sulfonated polyaniline compositions to have a fast switching speed between a conducting and a nonconducting state with good reversibility makes such compositions attractive polymers to use for a variety of electrochemical applications.

Applications contemplated by the present invention include but are not limited to the use of sulfonated polyaniline compositions for electrochromic displays where the composition's active response to a voltage step allows for a rapid change in color. Another application involves the use of sulfonated polyaniline compositions in active electronic devices such as switches and transistors. Yet other applications involve the use of sulfonated polyaniline compositions for charge storage or rechargeable battery applications since the sulfonated polyaniline compositions have excellent chemical stability along with good reversibility properties. The sulfonated polyaniline compositions are also useful as chemical sensors, wherein exposure to bases, acids, water and the like reactive chemicals causes a change in color of the composition and a change in the conductivity of the composition.

The solubility and the electrical conductivity of the sulfonated polyaniline compositions makes such compositions especially useful in still other applications. For example, other applications contemplated by the present invention are the uses of sulfonated polyaniline compositions as discharge layers for an electron beam lithography process and in use in forming patterns by such process. Still other applications include the use of sulfonated polyaniline compositions as electrical conductors, either in pure form or blended with other polymers such as Kevlar® and Nylon®, for use as a medium for electrostatic discharge in, for example device housings, and bulk coverings such as carpets and fabrics.

The sulfonated polyaniline compositions can be coated by a variety of techniques onto substrates of choice. The sulfonated polyaniline polymers can be

applied to substrates according to the present invention by spray coating, dip coating, spin casting, transfer roll coating, brush-on coating, and the like. The sulfonated polyaniline polymers can also be electrochemically deposited onto conductive substrates by known electrochemical deposition techniques.

5 Sulfonated polyaniline can also be entrained within a matrix of, or copolymerized with, other polymer materials to thereby produce a blend or a composite. Thus, sulfonated polyaniline could be dispersed in, for example, polyethylene, polyimide, cellulose nitrate, and the like, and also can be coated onto fibrous materials. The sulfonated polyaniline compositions can be used with
10 other insulating polymers to form conductive thermosetting resins, epoxies, and thermoplastics, and reacted with bismaleimides for use in forming, for example, such devices as conductive seals, joints and moldings. In addition, derivatization of the sulfonated polyaniline compositions can enhance compatibility and processability of the polymer with other polymers.

15 In addition, the sulfonated polyaniline compositions can be cast as thin films from a solvent solution, and the solvent evaporated to produce free standing films. The sulfonated polyaniline films can be stacked as a composite with other sulfonated polyaniline films, with films of sulfonated polyaniline copolymerized with another polymer, or with non-polyaniline polymers and/or
20 copolymers. Depending on the desired type and degree of substitution of the sulfonated polyaniline with various crosslinkable functional moieties, the films produced can be cured in deeper sections, that is, thicker films or articles can also be produced by known polymer preparation techniques.

25 The sulfonated polyaniline compositions and derivatives thereof have, or can be designed to have, desired processability in terms of, for example, viscosity, flexural strengths, solubility, adhesion to substrates, crosslinking, melting point, weight, adaptability to filler loading and the like. This is achieved by varying as desired the degree of self-protonation, the state of oxidation, and the type and degree of substituents on the polymer. Certain substituents may be
30 preferred for the facilitation of desired processing parameters, such as increasing or decreasing solubility, altering extrusion parameters (rheology), achieving a specific viscosity, and the like. Derivatization is also useful for achieving compatibility with a copolymer, facilitating the tunability of the sulfonated polyaniline composition for non-linear optics applications, and for
35 specific wavelength absorption, such as microwave attenuation or a particular photoresponse.

In another aspect of the present invention, the dielectric loss of the sulfonated polyaniline polymeric compositions can be controlled by the design of the chemical composition of the sulfonated polyaniline polymer, the oxidative state of the polymer, and the degree of self-doping or self-protonation of the polymer. Thus, by the addition of electron-withdrawing or electron-donating groups to the nitrogen atoms and/or the C₆ rings of the leucoemeraldine, emeraldine, or pernigraniline sulfonated polyaniline compositions, the dielectric loss tangent can be varied. The dielectric loss tangents can be varied from 10⁻² to approximately 20 by varying the form of the sulfonated polyaniline, the degree, site and type of substituents. In the prior art, carbon filled silicone rubber or carbon filled epoxy paints or carbon bonded to fabric produce non-magnetic dielectric losses at microwave frequencies. One embodiment of the present invention for attaining maximum dielectric loss is the emeraldine salt, wherein y is in the range of from approximately 0.4 to 0.6 and the protonation is approximately one proton per imine nitrogen, i.e., [H⁺]/[-N=] is equal to approximately one.

The addition of electron-withdrawing or electron-donating groups to the sulfonated polyaniline composition can facilitate the design of a polymeric material with desired absorption and transmission bands. The electron-withdrawing or electron-donating group can be present on the C₆ rings or the nitrogen atoms of the sulfonated polyaniline composition at any desired percentage of the available sites. Known electron-donating groups to be substituted onto the C₆ ring and operative in the present invention can include, but are not limited to, -OCH₃, -CH₃, -C₂H₅, halogens (electron-donating by way of a resonance effect), -NR₂, -NHCOR, -OH, -O⁻, -SR, -OR, and -OCOR, wherein R is a C₁-C₈ alkyl, aryl or aralkyl. These groups or atoms possess one or more unshared electron pairs on the atom adjacent to the ring. Known electron-withdrawing groups can include halogens (electron-withdrawing by way of an inductive effect), -NO₂, -COOH, -COOR, -COR, -CHO, and -CN, wherein R is a C₁-C₈ alkyl, aryl or aralkyl. Thus, the addition of electron-donating groups to the rings of sulfonated polyaniline augments the charge delocalization. The added opportunities for resonance stabilization of the pi to pi* excited state provided by electron-donating groups causes a lowering in the requirement for excitation energy, and thus a decreased frequency (longer wavelength) of absorption. Conversely, the addition of electron-withdrawing groups diminishes the opportunities for resonance stabilization, causing an increase in the requirement for excitation energy, and thus an increased frequency (shorter

wavelength) of absorption. Thus, for example, protonation of $-NH_2$ changes it to $-NH_3^+$; this group no longer has an unshared pair of electrons to participate in charge delocalization. Alteration of $-OH$ to the ion, $-O^-$, provides further opportunity for participation of unshared electrons on oxygen in charge delocalization. Thus, the change of H to NH_2 is bathochromic; NH_2 to NH_3^+ is hypsochromic; OH to O^- is bathochromic; and both of the changes, OH to $OCOCII_3$ and NH to $NHOCOCII_3$ (acetylation), are hypsochromic.

In this manner, a sulfonated polyaniline composition is prepared which when produced in a flexible sheet form or when it is coated onto a flexible substrate can be used to absorb electromagnetic radiation. Thus, a means of rendering an object undetectable to electromagnetic radiation such as radar is produced by the present invention by draping over the object the flexible sulfonated polyaniline film or the coated flexible substrate, such as a cloth fabric or fishnet. Furthermore, by coating electromagnetic radiation-absorbing sulfonated polyaniline compositions onto fibers, and then producing woven or non-woven fabrics from the coated fibers, cloth or clothing which is radiation absorbing can be produced. In another embodiment, fibers of sulfonated polyaniline itself or a derivative thereof, or fibers of sulfonated polyaniline copolymerized with another polymer can be drawn or extruded and subsequently woven into electromagnetic radiation absorbing fabric, garments, coverings, and the like. In this manner radar absorbing clothing can be produced.

Sulfonated polyaniline absorbs electromagnetic radiation in the visible spectrum, in the infrared range, and in the ultraviolet range. Thus, the present invention further relates to a method of absorbing infrared, visible, or ultraviolet waves comprising exposing the sulfonated polyaniline to infrared, visible or ultraviolet waves, whereby the infrared, visible, or ultraviolet waves are absorbed by the sulfonated polyaniline. The present invention also relates to a method for absorbing microwave radiation comprising exposing sulfonated polyaniline to microwave radiation, whereby the microwave radiation is absorbed by the sulfonated polyaniline.

The present invention also relates to a method of electromagnetic shielding. A thin film of sulfonated polyaniline within, for example, the walls of television sets, computers, electronic machinery, and places for the storage of electronic data, such as computer semiconductor memories, will effectively absorb continuous and intermittent electromagnetic radiation from wires, coils, cathode ray tubes and the like. Protection against unwanted or unknown electronic surveillance of rooms can be achieved by the application of

polyaniline to the walls, floors, and ceiling. Similarly, electrical wires can be shielded by the incorporation of a layer of sulfonated polyaniline material into the plastic insulator coating on the wires with the advantage of grounding and static free property.

5 In addition, sulfonated polyaniline can be used to make a remote thermal switch by exposing the sulfonated polyaniline composition to microwave radiation. The sulfonated polyaniline composition absorbs the radiation, which heats up the sulfonated polyaniline, which in turn, can trigger a thermocouple placed in contact with the sulfonated polyaniline composition. Upon removal of
10 the source of microwaves, the sulfonated polyaniline composition will cool and cause the thermocouple to switch back. By this manner a thermal switch is produced.

The present invention also relates to a sulfonated polyaniline composition for absorbing electromagnetic radiation, wherein said electromagnetic radiation
15 possess a wavelength generally in the range of from about 1000 Angstroms to about 50 meters, wherein the composition comprises a sulfonated polyaniline composition of the formula I, above, or a protonated salt thereof, where y is in the range of approximately 0.2 to 0.8, and the degree of protonation, i.e., $[H^+]/[-N=]$, varies from 0 through 1.

20 The present invention further relates to a method of applying heat to a substrate which comprising the steps of: (a) applying to a substrate a microwave radiation-absorbing sulfonated polyaniline composition, or a partially self-protonated salt thereof; and (b) exposing the microwave radiation-absorbing
25 sulfonated polyaniline composition, for example, a partially self-protonated salt thereof, to microwave radiation, whereby the microwave radiation-absorbing sulfonated polyaniline composition, or the partially self-protonated salt thereof, absorbs the microwave radiation, resulting in the generation of thermal energy within the sulfonated polyaniline composition. This heat can be localized,
30 transferred from the sulfonated polyaniline composition or the salt to a substrate and utilized to accomplish desired results, such as, but not limited to, joining of materials. Thus, two materials which have been placed in contact or close proximity with each other and in contact with a sulfonated polyaniline composition can be adhered to each other upon the exposure of the sulfonated
35 polyaniline composition to sufficient microwave radiation to heat and thus melt or at least soften at least one of the materials to enable fusing. The frequency, duration and/or intensity of the microwave radiation necessary to achieve the desired adhesion of the two materials will vary depending on the nature of the

materials to be adhered and on the degree and type of protonation and/or substitution, if any, on the sulfonated polyaniline. The preferred frequency of the microwave radiation to be absorbed by the sulfonated polyaniline compositions to thereby induce localized heating is from about 10^9 Hz to about 5 10^{11} Hz. The sulfonated polyaniline composition can be applied to one or both of the materials in any pattern, such as a grid pattern, stripes, spots, or the like as desired. The sulfonated polyaniline can be applied via solution coating, adhesion of films, vapor deposition, extrusion of gels containing sulfonate polyaniline and other known application techniques.

10 In one embodiment of the present invention directed toward the adhering of two or more materials by the absorption of microwave radiation by sulfonated polyaniline, at least one of the materials to be adhered is a plastic. In another embodiment, one of the materials to be adhered is a silicate-containing material, 15 such as, for example quartz or glass. In this manner, a plastic can be adhered to a glass fiber, such as an optical fiber, by means of exposure of the sulfonated polyaniline to microwave radiation.

Sulfonated polyaniline compositions can also be utilized to absorb radar waves possessing a wavelength in the general range of from about 0.01cm to about 100cm. The absorption of radar waves by the sulfonated polyaniline 20 composition assists in rendering objects coated with the sulfonated polyaniline composition relatively invisible to radar detection. Therefore, the instant invention further relates to a method for absorbing radar waves comprising exposing a sulfonated polyaniline composition or a partially protonated salt thereof to radar waves whereby the sulfonated polyaniline composition or the 25 salt thereof absorbs at least some of the radar waves. The invention further relates to a method for reducing the detectability by radar of an object comprising applying to the object a sulfonated polyaniline composition or a partially self-protonated salt thereof in an amount sufficient to absorb at least some, and preferably all, radar radiation to which the object may be exposed.

30 In one embodiment of the method for reducing the detectability by radar of an object it is desirable to coat the object in such a way as to produce a gradient of absorption to minimize reflectance. Such a gradient of sulfonated polyaniline material can be achieved by varying the degree of self-protonation of the polymer or the degree of substitution on either the C_6 ring or the nitrogen atoms 35 or both with a chemical substituent such that an incoming radar beam first encounters a sulfonated polyaniline composition with little or no self-protonation, i.e., a material with limited absorption of radiation. As the beam

further advances along the gradient of sulfonated polyaniline material covering the object, the beam encounters sulfonated polyaniline polymer with continually increasing degrees of self-protonation, and hence increasing degrees of electromagnetic absorption. The gradient of self-protonation can be controlled
5 through the gradient of sulfonation. In this manner, little or no reflection of the beam is produced and the object is not detectable by a radar wave reflection.

The present invention further relates to a method of electrochemical switching of the polymeric state of a sulfonated polyaniline composition. By contacting the sulfonated polyaniline composition with an electrolyte,
10 electrochemical switching of the polymeric state can be significantly accelerated, being accomplished on a time scale of approximately 10^{-5} seconds. By contacting the sulfonated polyaniline composition with a solid electrolyte, electrochemical switching of the polymeric state can be even further
15 accelerated, being accomplished on a time scale of less than approximately 10^{-7} seconds particularly since only protons need migrate in the sulfonated polyaniline compositions. For electromagnetic radiation absorption, such as the absorption of microwave radiation, electrochemical switching of the polymeric state can
20 turn the polymeric material from radiation transparent to radiation absorbing, or vice versa, depending on the nature and direction of the electrochemical switching. For non-linear optics, electrochemical switching can change the important absorption and/or transmission bands for the probe and modulator
25 beams, such as for example, in switching from the emeraldine base form to the emeraldine salt form of sulfonated polyaniline. The range of the absorption bands for the base and the salt can be shifted bathochromically (i.e., shifted to longer wavelengths) or hypsochromically (i.e., shifted to shorter wavelengths) as
30 may be desired according to the characteristics of the available probe beam, the available modulator beam, or the available detector or sensor, or any combination thereof.

Sulfonated polyaniline compositions can also be used as a photoactive
35 switch by manipulation of the index of refraction of the sulfonated polyaniline compositions. The extremely rapid photoresponse of the sulfonated polyaniline polymer, makes such polymer useful in nonlinear optical devices. The time dependence of the photo bleaching of the polymer is on the order of picoseconds. For example, the application of a laser beam of wavelength 6200 Angstroms
40 (2.0eV) to sulfonated polyaniline polymer produces significant photoinduced bleaching (i.e., increased transmission) in broad energy bands of 8,265 Angstroms to 4,590 Angstroms (approximately 1.5eV to 2.7eV) and again at 3,760 Angstroms

to 2,880 Angstroms (approximately 3.3eV to 4.3eV). Simultaneously laser beam photoinduced absorption (i.e., decreased transmission) for sulfonated polyaniline occurs at 24,800 Angstroms to 8,265 Angstroms (approximately 0.5eV to 1.5eV) and from 4,590 Angstroms to 3,760 Angstroms (2.7eV to 3.3eV). Photoinduced
5 absorption and bleaching occur in sulfonated polyaniline compositions in less than 10-12 seconds. These photoinduced changes in absorption correspond to changes in the index of refraction at these wavelengths. These changes in optical constants have broad application in nonlinear optical signal processing and optical communications, which according to the present invention, are useful as
10 means to switch, modulate, multiplex, focus, and provide optical bistability for commercial systems.

Sulfonated polyaniline is therefore useful in nonlinear optical signal processing. For example, a thin film coating of sulfonated polyaniline can be applied to a phototransmissive substrate. In one embodiment of the present
15 invention, a probe beam of light of a given wavelength is then propagated through the noncoated side of the substrate onto the coating at the critical angle to the sulfonated polyaniline such that the probe beam is wave-guided in the phototransmissive substrate. To activate the desired switching property of the sulfonated polyaniline coating, a pump beam of light, also called a modulator, of
20 a different wavelength or some wavelength is applied to the coating through the coated or noncoated side of the substrate at a second angle such that the index of refraction of the sulfonated polyaniline composition is changed by the absorption by the sulfonated polyaniline of the electromagnetic radiation of the modulator beam. The wavelength of the modulator beam can vary widely, but is
25 preferably within the range of from about 8265 Angstroms (1.5eV) to about 4590 Angstroms (2.7eV). The change in the refractive index of the sulfonated polyaniline composition coating alters the transmissive property of the sulfonated polyaniline and allows the probe beam to be refracted or otherwise modified by the sulfonated polyaniline coating. This refraction or other
30 modification of the probe beam can, for example, be used to trigger a photocell, initiate or terminate an optical signal, encode information on the probe beam, or the like. By these means is produced a low cost, stable means of optical signal processing.

In an alternative embodiment, the beam to be modulated is refracted by
35 the phototransmissive substrate and reflected off the sulfonated polyaniline coating on the backside of the substrate such that the beam is then reflected repeatedly between the front side of the substrate and the sulfonated polyaniline

coated backside of the substrate. This reflection continues within the phototransmissive substrate until the modulating beam is caused to impinge on the sulfonated polyaniline coating, whereby the index of refraction of the sulfonated polyaniline coating is altered by the absorption of the electromagnetic radiation of the modulator beam, altering the propagation of the probe beam. In this manner the sulfonated polyaniline coating has acted as a switch which is reversibly controlled by the presence of the pump or modulating beam to increase or decrease the modulation (both intensity and direction) of the probe beam. Because of the very rapid photoresponse rate of the sulfonated polyaniline polymer, the refractive index can be altered at gigahertz to terrahertz rates, thereby providing a method for the rapid modulation of optical data signals.

In yet another embodiment, the beam to be modulated is caused to impinge upon a thin coating of sulfonated polyaniline which is on a phototransmissive substrate. A portion of the beam is reflected, the remainder refracted, transmitted, and partly absorbed. Application of a modulator beam at a second angle changes the index of refraction of the sulfonated polyaniline thereby altering the direction and the percentage of the probe beam transmitted and reflected.

Thus, the present invention further relates to a method of changing the refractive index of sulfonated polyaniline comprising (a) applying sulfonated polyaniline to a phototransmissive substrate; (b) applying a first beam of light of wavelength x at the critical angle y to the sulfonated polyaniline surface; and, (c) applying a second beam of light of wavelength z to the sulfonated polyaniline surface, whereby the second beam is absorbed by the sulfonated polyaniline changing the index of refraction of the sulfonated polyaniline, whereby the transmission of the first beam through the phototransmissive substrate is altered. The preferred wavelength x of the first or probe beam of light is dependent on the form of sulfonated polyaniline utilized. The preferred wavelengths will vary depending on the degree of self-protonation and oxidative state of the sulfonated polyaniline polymer and the nature of the substituents, if any, on the polymer. The preferred wavelength of the second or modulating beam is determined by the oxidation state, self-protonation level, and substituents of the polymer. For the leucoemeraldine polymer the preferred wavelengths of the probe beam are in the range of 24,800 Angstroms to 8,265 Angstroms (0.5 to 1.5eV) and 4,590 Angstroms and 3,760 Angstroms 2.70 to 3.30eV, with greater preferred modulator beam wavelength of 3,760 Angstroms

to 2,880 Angstroms, 3.30 to 4.30eV. For pernigraniline base, the preferred probe and modulator wavelength are similar to those of emeraldine base.

The photoswitching phenomenon can, according to the present invention, also be used to couple a light signal from one optical fiber to another optical
5 fiber. The two optical fibers are positioned in close contact with each other and with a thin film of sulfonated polyaniline composition between them. The sulfonated polyaniline composition is then exposed to a modulating beam. The modulating beam changes the index of refraction of the sulfonated polyaniline such that "crosstalk" between two optical fibers is obtained. This allows the
10 optical signal within either of the optical fibers to be coupled to the other fiber as desired, but without permanent physical alteration of either fiber. In addition, the coupling can be turned on and off as desired by the manipulation of the index of refraction and, because of the very rapid photoresponse rate of the sulfonated polyaniline polymer, the refractive index can be altered and coupling
15 achieved at gigahertz to terrahertz rates.

In yet another embodiment of the present invention the sulfonated polyaniline composition can itself be utilized simultaneously as the phototransmissive material and a photoswitch without a phototransmissive
20 substrate. Thus, a free standing sulfonated polyaniline polymer can be exposed to a first beam of light which will be transmitted through the sulfonated polyaniline with some attenuation. When the polymer is exposed to a second or modulator beam the refractive index and absorption coefficient of the sulfonated polyaniline polymer are altered, changing the intensity and angle of refraction of the beam transmitted through the polymer.

25 Another embodiment of the present invention is the use of sulfonated polyaniline compositions as a masking material over ultraviolet-curable polymers in the fabrication of positive resist and negative resist microelectronic devices and circuits. In the fabrication of certain positive resist and negative resist microelectronic devices and circuits, radiation curable polymers are deposited on
30 conductive or semiconductive surfaces, such as silicon or doped silicon. A circuit pattern is then applied by means of photolithographic techniques and covered by ultraviolet-curable polymers in certain desired patterns. Ultraviolet radiation is then applied to the polymers to cure certain portions, after which the uncured portions are removed by solvent rinsing, for example. In this
35 manner, patterns of cured polymer are provided on the conductive or semiconductive surfaces. By the present invention, sulfonated polyaniline can be applied to the curable polymer in a predetermined pattern such that the polymer

beneath the sulfonated polyaniline pattern is desired to remain uncured upon exposure of the coated device or circuit to radiation. When the polymer is exposed to the radiation, the sulfonated polyaniline would absorb the ultraviolet radiation to thereby mask the polymer and prevent the cure in certain locations
5 of the curable polymer beneath.

Thus, the present invention relates to a method for masking a radiation curable polymer applied to an electronic circuit or device comprising the steps of (a) applying a radiation-curable polymer or prepolymer to an electronic device or circuit; (b) applying to the radiation-curable polymer or prepolymer a
10 sulfonated polyaniline composition; (c) exposing the device or circuit with the curable polymer or prepolymer and the sulfonated polyaniline composition to radiation sufficient to cure the curable polymer or prepolymer and whereby the sulfonated polyaniline composition absorbs some of the ultraviolet radiation; and
15 (d) removing the sulfonated polyaniline and any uncured curable polymer or prepolymer. In a preferred embodiment of the invention, the curable polymer or prepolymer and the sulfonated polyaniline are independently deposited onto the surface of the electronic device or circuit by means of a solvent solution of each material, followed by the evaporation of the solvent. By "cure" herein is meant
20 sufficient coreaction and/or crosslinking reactions have taken place to render the material a solid not easily removed by solvent.

The present invention further relates to various devices such as optical devices and microwave devices which utilize the features, characteristics and properties of the sulfonated polyaniline compounds which are described above.

The optical devices are useful in a range of electromagnetic spectrum at or
25 near what is commonly referred to as light. These devices utilize the fact that the index of refraction of the sulfonated polyaniline compounds may be controlled by varying the intensity and wavelength of light radiated upon the sulfonated polyaniline compound. Thus, a pumping or modulating light at one or a broad band of frequencies may be used to modulate the index of refraction of
30 the sulfonated polyaniline compound and thereby modulate light at another frequency. For example, this can be used for the coupling of the modulated light from one light transmissive medium to another or modulating its angle of departure from an interface between two light transmitting media. The spectral response of this photo effect is substantially changed as the compounds are more
35 fully self-protonated.

The present invention also relates to devices which can operate as various types of light valves, as a phase velocity modulator and for controlling the angle

of emission of a light beam. The light valves may be light switches turning the modulated beam on or off or variable valves which permit the intensity of the modulated light beam to be varied continuously over a range by varying the intensity of the modulating light beam. In a valve the modulating light beam
5 pumps the electrons into higher energy bands causing the critical angle for a light beam incident upon an interface to be increased for some frequency bands and decreased for other bands as the intensity of the pump or modulating light increases.

Fig. 9 illustrates one such device. It has a substrate supporting a
10 sulfonated polyaniline mass in the form of a film bonded to the substrate. The interface between the sulfonated polyaniline film and the air will have a critical angle of, for example, C_1 when a modulating light does not pump the sulfonated polyaniline film and a critical angle C_2 when the modulating light is intense. The angles are greatly exaggerated for illustration. In this example when the
15 modulating light does not pump the sulfonated polyaniline film, a light beam which is incident upon the sulfonated polyaniline film at an angle greater than the critical angle C_1 will not be substantially transmitted into the film but instead will be reflected along a path. However, when the modulating beam is turned on for pumping, the critical angle increases to angle C_2 thus permitting
20 the coupling of light from the beam into the film.

The critical angle is increased by an increase in the intensity of the modulating beam for some frequency ranges of incident modulated light and is decreased for others. Thus, the illustration of Fig. 9 continues to be accurate for all events. However, for some frequencies of incident, modulated beam, the
25 critical angle when the sulfonated polyaniline is not pumped is the greater angle and then decreases to C_1 as pumping energy is increased.

The result is that the incident light beam is always substantially equal to the critical angle being either slightly greater or lesser than the precise critical angle depending upon the incident beam frequency. Thus, the structure can be
30 used to that increasing the intensity of the pumping, modulating beam will turn off the coupling of light from one transmission medium to another for some optical bands while turning on the coupling for other bands.

Fig. 10 illustrates a structure utilizing the same principles as illustrated in Fig. 9 but for coupling the light from a sulfonated polyaniline film into another
35 light transmissive substrate. However, in the structure of Fig. 9, the interface at which the critical angle is important is the interface between the sulfonated polyaniline film and the light transmissive substrate. Thus, in the embodiment of

Fig. 10 an incident light beam must be incident at an angle such that after it enters the sulfonated polyaniline film and is refracted along a different path it will approach the interface between the sulfonated polyaniline film and the transmissive substrate at substantially the critical angle, being greater or lesser than the critical angle by a smaller amount in accordance with the principles described in connection with Fig. 9. The coupling of light from the sulfonated polyaniline layer to the substrate layer is thus controlled by a modulating light. From the above description it is apparent that a beam in the opposite direction may also be similarly controlled.

Fig. 11 illustrates another embodiment similar to the embodiment of Figs. 9 and 10. In Fig. 11, however, an optical fiber light conductor has a sulfonated polyaniline layer upon at least a portion of its outer longitudinal surface. In this manner a pumping light can control the coupling of an incident light beam into the optical fiber light conductor.

Fig. 12 illustrates an optical fiber having an endface which is lapped at substantially the critical angle for the interface between the optical fiber and a sulfonated polyaniline film coated on the lapped endface. An incident light beam may be directed upon the sulfonated polyaniline film parallel to the longitudinal optical axis of the optical fiber. The device operates on the same principles described in connection with Figs. 9 and 10 except the light beam when coupled into the optical fiber enters along the longitudinal optical axis.

Figs. 13 and 14 illustrate yet another device in which a pair of optical fibers are controllably coupled together by an interposed sulfonated polyaniline film joining the two fibers. Together these form three light conducting media. An input light beam propagating along the first fiber enters the region along which the sulfonated polyaniline is distributed. The coupling of light into the sulfonated polyaniline and into the second optical fiber is controlled by a pumping beam so that some of the light from input light is coupled into the second optical fiber to provide an output light. Fig. 15 illustrates a Mach Zehnder interferometer made up of light conductors in which an input light beam arrives in an optical fiber and is divided into a first branch and a second branch. These two branches are recombined at the optical output fiber. In accordance with the principles of the prior art Mach Zehnder interferometer, if the two beams arrive in phase in the output fiber they constructively interfere and the light beam and any associated signal continues along the path. However, if the beams destructively interfere, the light beam is destroyed. By variably controlling or altering the phase velocity through the second branch, the relative

phases of the two light signals recombining at output optical fiber may be controllably varied between constructive and destructive interference.

While the Mach Zehnder interferometer is old and known, we have found a new manner of controlling the phase velocity in the second branch. The second
5 branch is coated with a layer of the photo responsive sulfonated polyaniline film. A variable intensity pumping light for modulating the index of refraction of that layer is used to control the phase velocity of the light through the second branch. Thus, varying the intensity of the modulating or pumping light changes the phase
10 velocity in the second branch and therefore changes the phase relationship between the two arriving signals in the output fiber.

The microwave devices of the present invention arise because we have discovered that a highly self-protonated emeraldine salt polymer has a high dielectric loss which we attribute to its combination of a modest conductivity
15 and a high dielectric constant. The loss tangent, a quantitative indication of the energy loss in the polymer, is a function of the self-protonation level of the polymer and increase as the self-protonation level increases reaching a maximum at complete 50% protonation. Very importantly, the self-protonation level may be controlled as described above in the synthesizing of the material and also may
20 be varied by changing the potential by means of an electrochemical cell. This permits the polymers to be made with a variety of selected loss tangents and further permits the loss tangents of the polymers to be variably controlled in a variety of useful devices. For example, the microwave properties may be turned on and off or varied over a range.

In Figs. 16 and 17 a layer of self-protonated sulfonated polyaniline is
25 bonded to the interior walls of a wave guide. As the microwave propagates from an input end to an output end, it is attenuated in the sulfonated polyaniline layer. This layer may be formed with a continuously changing self-protonation level along the propagation axis of the wave guide to provide a selected self-protonation gradient and therefore loss gradient between the input end and
30 output end. This gradient can be contoured to minimize reflections where the propagating microwave encounters the transition from an absence of sulfonated polyaniline layer to the presence of the layer. Additionally, the layer may be geometrically formed to gradually taper to a greater thickness as the microwave propagates from the input end to the outlet end.

35 Fig. 13 illustrates a similar wave guide having a mass of sulfonated polyaniline so that it has a geometrical configuration providing an increase in thickness, that is an increase in its cross-sectional area in planes perpendicular to the axis of propagation.

Fig. 19 illustrates another embodiment of the invention in which the sulfonated polyaniline mass is positioned within the interior of a wave guide and also extends between its walls. In the interior of the embodiment of Fig. 19 there is positioned a plurality of laminated layers of sulfonated polyaniline each layer having a different self-protonated level. This structure is particularly suitable for terminating an end of a wave guide in a manner to prevent reflections. Other circuitry may be used to direct unwanted microwave energy, for example, into the illustrated wave guide where it can be effectively attenuated. In order to minimize reflections, as described above, the layers initially encountered by the incoming microwave are the least self-protonated so they are the less absorptive. The layers become increasingly more self-protonated and therefore more absorptive as they are positioned closer to the end of the wave guide. Preferably, the average gradient of the variation in self-protonation and therefore in the variation in absorption is a monotonically increasing function of distance along the propagation axis.

Referring to Fig. 20, if it is desired to prevent reflections of microwave energy from a metallic or other reflective surface, the surface may be coated with a sulfonated polyaniline layer which is provided with a self-protonation gradient which increases from near 0% at the exposed outer surface to a much greater level, 50% for example, at an interface between the reflection surface and the sulfonated polyaniline layer.

Similarly, as illustrated in Figs. 21, 22 and 23 the sulfonated polyaniline absorptive layer may be bonded to the exterior surface of a microwave strip conductor. This provides a convenient means for introducing attenuation onto a microwave strip conductor used in miniature or integrated circuits while minimizing reflections from it. For example, a sulfonated polyaniline layer can be synthesized as described above so that it has a variation in its self-protonation as a function of its position or distance along the axis of propagation of the strip conductor. The self-protonation varies from a minimum self-protonation level at its opposite end regions and increasing towards a central region to a maximum self-protonation at the central region.

Fig. 22 illustrates use of sulfonated polyaniline as a terminating absorber on an end of a branch of the microwave strip conductor. The sulfonated polyaniline layer is formed with a self-protonation gradient extending from a minimum self-protonation at its input end to a maximum self-protonation at its terminating end.

The gradual variation in the microwave loss tangent so that absorption increases gradually from the input end to the opposite end along the propagation axis may alternatively be accomplished or may be supplemented by increasing the thickness of the sulfonated polyaniline layer to also increase energy
5 absorption.

One major advantage of sulfonated polyaniline materials used in the present invention is that their self-protonation and therefore their absorption or loss tangent may be controlled by an electrical potential. This feature may be utilized in many various embodiments of the invention but is illustrated in Fig.
10 23.

Fig. 23 illustrates a microwave strip conductor upon which a sulfonated polyaniline layer is positioned of the type illustrated in Fig. 21. The strip may, if desired, have a protonation or a thickness gradient. This layer, because it is also
15 conductive, may also serve as one electrode of an electrochemical cell. It is connected to a variable potential. The other terminal of the variable potential is connected to another electrode of this electrochemical cell. A solid or liquid electrolyte is positioned between the electrodes. Thus, the application of the variable potential permits the potential of the sulfonated polyaniline to be varied, controlling or varying its self-protonation as a function of the potential
20 and thereby varying its absorption or loss tangent. In this manner, the effect of the sulfonated polyaniline layer may be switched on and off by switching the sulfonated polyaniline between fully self-protonated and unprotonated states and may be varied to intermediate levels of self-protonation.

Fig. 24 illustrates a structure for controlling and varying the self-protonation gradient along a microwave strip conductor by forming the sulfonated polyaniline layer into a series of discrete segments along the axis of propagation of the microwaves. Each individual sulfonated polyaniline segment
25 forms an electrode of a separate electrochemical cell. Each of these cells has a second electrode, for example, and an interposed electrolyte like the electrolyte in Fig. 23 but separately associated with each individual electrochemical cell. A separate potential is applied for controllably varying the potential of each discrete segment of sulfonated polyaniline mass along the propagation axis so
30 that its loss tangent may be independently varied. Different potentials may be applied to each of these discrete cells to controllably contour the self-protonation gradient which is desired for particular circumstances.
35

Figs. 25 and 26 illustrate embodiments in which a thermally responsive film has microwave radiation absorbing self-protonated sulfonated polyaniline

polymer in the emeraldine salt state distributed in the thermally responsive film. The term "distributed" is intended to include the various chemical techniques for distributing the active materials in a thermally responsive film material, this includes dispersing and copolymerization. This distribution of the microwave radiation absorbing polymer in the thermally responsive film permits the film to be activated by microwave energy rather than by radiation with infrared energy. This is particularly useful in electrically insulative environments in which the energy may be coupled specifically into the thermally responsive film without undue heating of surrounding structure and from a remote source.

For example, if the principal carrier film is a thermally deformable film such as thermoplastic film which softens and flows more easily when heated, it may be used to form a barrier or closure which can be destroyed from a remote position by irradiation with microwave energy. For example, Fig. 25 illustrates a conduit having a thermoplastic film with microwave radiation absorbing self-protonated sulfonated polyaniline salt polymer distributed within it to form a barrier between the conduits. This sealing film will block passage of fluids, for example, past the barrier formed by the film until the film is radiated by microwave energy causing the barrier to be heated, softened and eventually separate to open the passage.

The microwave radiation absorbing self-protonated sulfonated polyaniline salt polymer may also be distributed in or copolymerized with a conventional thermally activated shrink wrap film. For example, Fig. 26 illustrates a conduit having a defect or crack. A thermoplastic film with microwave radiation absorbing self-protonated sulfonated polyaniline salt polymer distributed with it is loosely wrapped around the conduit and the film is then irradiated with microwave energy causing the sulfonated polyaniline polymer to absorb the microwave energy convert it to heat thereby heating the film and activating its shrink properties.

The microwave absorptive sulfonated polyaniline film can be advantageously used for shielding objects as mentioned above and is particularly useful for shielding a plurality of electrical conductors to form a shielded cable. The sulfonated polyaniline shield not only prevents electromagnetic energy from entering the cable and thereby coupling noise into the conductors and prevents electromagnetic energy from exiting the cable but additionally because the sulfonated polyaniline is also conductive, the outer conducting sulfonated polyaniline shield may also be used to ground an electronic device to which it is connected. Thus, because the sulfonated polyaniline is also conductive, it may

not only absorb rather than merely reflect the microwave energy but it may also conduct current to maintain an electrical apparatus at a ground potential.

5 The ability to permanently alter at will the absorption characteristics of sulfonated polyaniline through the application of light or electrochemical potential provides a powerful technology for use in information storage.

10 Transmission characteristics of the photoinduced absorption in sulfonated polyaniline are also dependent upon the writing laser input intensity. That is, the amount of photoinduced absorption is proportional to the intensity of the writing laser. This ability to "stack" the transmission characteristics of the shifted photoabsorption spectrum of sulfonated polyaniline provides the capability to "stack" information storage at one given bit location on a storage unit. Thus, the read lasers can be utilized to correspond to the laser input intensity to read three-dimensionally at one bit location of the storage system.

15 Chemical or electrochemical erasure of the stored information in a total or bit-wise manner is possible by temporary conversion of the insulating forms of sulfonated polyaniline to the conducting form of the sulfonated polyaniline film. Similarly, if information storage is carried out using the long lived photoinduced absorption of the conducting forms of sulfonated polyaniline, then total or bitwise erasure can occur by chemical or electrochemical conversion to one of
20 the insulating (leucoemeraldine, emeraldine or pernigraniline) forms of the polymer. Electrochemical conversion is achieved in a compact solid-state sandwich cell such as shown in Fig. 27 and Fig. 28. The sandwich cell incorporates a solid electrolyte such as polyethyleneoxide and at least one transparent or semi-transparent electrode. The electrochemical electrodes are
25 arranged in two overlaid but electrically isolated raster-like arrays. Applying voltage to two electrically conducting strips that cross at bit element P would produce a large enough voltage to switch the spectral state of the polymer at that bit element P. Application of a voltage at only one such would be insufficient to switch the bit. In addition to enabling the electrical erasure or
30 correction of individual bits written optically this also allows the use of electrical bit data to write to the polymer and subsequently bring rapid optical read of the stored information.

35 The temperature for erasure of the photoinduced information is one of sulfonated controllable by judicious choice of the N or ring substituent. For example, use of polyortho-toluidine and naphthal versions of sulfonated polyaniline in the emeraldine equivalent oxidation state polyaniline will provide stability to higher temperatures, likely exceeding room temperature. Hence,

- 40 -

some of these derivative systems will be usable at room temperature, with erasure occurring above room temperature.

The sulfonated polyaniline medium used for information storage may also be combined in composite form with other polymers to blend mechanical and optical storage function. The density of optical storage is limited only by the diffraction limits of the writing and probing beams utilized. Assuming a wavelength of 500nm ultimately of bit density of approximately 1 bit per 1 micron by 1 micron square or approximately 7.3×10^{10} bit per 12 inch diameter disk is obtainable. Use of a shorter wavelength light or finer focusing technique leads to an even higher density of optical storage. This is 1000 times the information density available in current commercial technologies. This estimate is obtained assuming that each bit is either "on" (1, photoinduced absorption is present) or "off" (0, no photoinduced absorption present). Discriminating two levels of photoinduced absorption, for example reading each bit as 0, 1, 2, raises the total information storage capacity dramatically.

Fig. 29 is a schematic illustration of sulfonated polyaniline containing an optical disk device incorporating a rotating optical disk, laser and mirror for writing bits of information, and laser and mirror for reading the photoinduced information. A third laser (shown) and mirror may be added for bit-wise erasure purposes. It is noted that these mirrors may be replaced by self-focusing lenses, rotating polygon mirrors, or other available devices for directing the light emitting from these lasers to the desired bit track on the rotating disk. The detector moves in a coordinated fashion to lie under the bit being probed or alternatively the collection optics (including mirrors, etc.) track the bit being selected and guide the collective light to the detector. The output of the detector is discriminated to distinguish more than one level of information stored within the bit location.

The multi-level information storage aspect of the present invention can be alternatively achieved through the use of an optical disk having two oriented films of sulfonated polyaniline held at 90° relative orientation. Write, read, and erase light beams polarized parallel to the orientation direction of the top layer will record, read, and erase information on the top layer; light polarized parallel to the orientation direction of the bottom layer will be transmitted through the top layer and will record, read, and erase the bottom layer.

Fig. 30 is a schematic representation of the use of sulfonated polyaniline film to produce holographic images and photoinduced grating in a two-dimensional framework is shown. The two-dimensional framework is the sample

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configuration of a sulfonated polyaniline film supported by a transparent substrate. Two beams I_1 and I_2 interfere in the sulfonated polyaniline film to form an interference pattern or holographic image within the polymer.

5 Fig. 31 shows a three-dimensional holographic and photoinduced grating application by schematic illustration. A thick sample of sulfonated polyaniline or sulfonated polyaniline dispersed in a transparent host polymer such as kapton or polycarbonate is used. In this illustration two beams I_1 and I_2 , interfere in the sulfonated polyaniline film to form an interference pattern or holographic image within the polymer.

10 The sulfonated polyaniline for use in photorefractive applications as envisioned in either Fig. 30 or 31 has an advantage over usual photorefractive materials such as $\text{Bi}_{12}\text{SiO}_{20}$ crystals in that the latter systems require applications of high voltage (6kVcm^{-1}) to the photorefractive material to maintain the photoinduced grating or holographic image. The sulfonated
15 polyaniline material, because of the different microscopic mechanism involved, does not require the application of voltage to produce this high electric field, with concomitant advantages in design simplification, fabrication and processing simplification, and cost reduction.

20 While the invention has been disclosed in this patent application by reference to the details of preferred embodiments and examples of the invention, it is to be understood that this disclosure is intended in an illustrative rather than in a limiting sense, as it is contemplated that modifications will readily occur to those skilled in the art, within the spirit of the invention and the scope of the claims which follow.

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30

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Table 1: Elemental Analyses^a of Chemically Synthesized Sulfonic Ring-Substituted Polyaniline

sample	C	H	N	S	O ^b	Total	Formula
aniline(cal.)	77.38	7.58	15.04	—	—	100	C ₆ H ₇ N
PAN(cal.)	79.54	5.00	15.46	—	—	100	C ₁₂ H ₉ N
PAN(found)	79.14	4.96	15.16	—	—	99.26	C ₁₂ H ₉ N
SPAN(cal.)	55.16	3.47	10.72	12.27	18.37	100.00	C ₁₂ H ₉ N ₂ SO ₃
SPAN(found)	54.98	3.40	10.68	11.85	17.77	98.68	C ₁₂ H ₉ N ₂ S ₁ O ₃ ^c

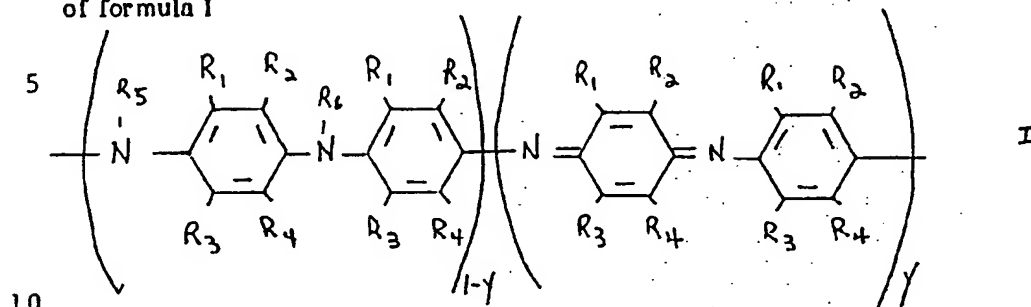
a C, H, and N analyses were performed by Dr. R. Kohli at U. of Pennsylvania, S analysis was carried out by M-II-W Laboratories, Phoenix, AZ.

b Oxygen content was found by assuming three oxygen atoms for every sulfur atom.

c Ratio of H, N, and S to C corresponds to experimental value of C₁₂H_{8.8}N_{1.98}S_{0.97}O_{2.9}.

CLAIMS:

1. A sulfonated polyaniline composition having a chemical composition of formula I



wherein $0 \leq y \leq 1$, R_1, R_2, R_3, R_4, R_5 and R_6 are independently selected from the group consisting of H, SO_3^- , $-\text{SO}_3\text{H}$, $-\text{R}_7\text{SO}_3^-$, $-\text{R}_7\text{SO}_3\text{H}$, $-\text{OCH}_3$, $-\text{CH}_3$, $-\text{C}_2\text{H}_5$, $-\text{F}$, $-\text{Cl}$, $-\text{Br}$, $-\text{I}$, $-\text{NR}_7$, $-\text{NHCOR}_7$, $-\text{OH}$, $-\text{O}^-$, $-\text{SR}_7$, $-\text{OR}_7$, $-\text{OCOR}_7$, $-\text{NO}_2$, $-\text{COOH}$, $-\text{COOR}_7$, $-\text{COR}_7$, $-\text{CHO}$ and $-\text{CN}$, wherein R_7 is a C_1 - C_8 alkyl, aryl or aralkyl group, and wherein the fraction of rings containing at least one R_1, R_2, R_3 or R_4 group being an $-\text{SO}_3^-$, $-\text{SO}_3\text{H}$, $-\text{R}_7\text{SO}_3^-$, or $-\text{R}_7\text{SO}_3\text{H}$ varies from approximately 20 percent to one hundred percent.

2. The composition as claimed in claim 1, wherein the sulfonated polyaniline composition is of molecular weight in the range of from approximately 300 (oligomers of sulfonated polyaniline) to in excess of 100,000.

3. The composition as claimed in claim 1, wherein R_1 is selected from the group consisting of $-\text{SO}_3^-$, $-\text{SO}_3\text{H}$, $-\text{R}_7\text{SO}_3^-$, and $-\text{R}_7\text{SO}_3\text{H}$ and $R_2 = R_3 = R_4 = \text{H}$ and $y \sim 0.5$.

4. A process for producing the polyaniline composition of claim 1 comprising reacting a polyaniline polymer and H_2SO_4 .

5. The process according to claim 4 in which the reaction is conducted at a temperature range of between about -38°C and 100°C .

6. The process according to claim 4 in which the reaction is carried out in air.

7. The process according to claim 4 in which the polyaniline polymer has a predetermined chain length which is not reduced in length during the reaction.

8. The process according to claim 4 in which a copolymer of polyaniline and sulfonated polyaniline is obtained by partially sulfonating the polyaniline polymer.
- 5
9. The process according to claim 8 in which the partial sulfonation of the polyaniline polymer comprises shortening sulfonation times and/or lowering sulfonation temperatures.
- 10
10. The process according to claim 4 in which a copolymer of polyaniline and sulfonated polyaniline are obtained by reacting 2-amino-sulfonic acid and aniline with an oxidizing agent comprising potassium persulfate in an acidic aqueous solution.
- 15
11. A composition for switching an electrochemical response between a conducting and a nonconducting state, wherein the electrochemical response is in the range of about -0.2 to about 0.8V, wherein the composition comprises a sulfonated polyaniline composition of the formula I.
- 20
12. The composition as claimed in claim 11, wherein the composition is used in an electrochromic display.
13. The composition as claimed in claim 11, wherein the composition is used in an electronic switch.
- 25
14. The composition as claimed in claim 11, wherein the composition is used in a rechargeable battery.
15. A method for switching an electrochemical response between a
- 30
- conducting and a nonconducting state comprising varying the applied potential to a sulfonated polyaniline of the formula I, whereby the electrochemical response in the sulfonated polyaniline composition switches between a conducting and nonconducting state.
- 35
16. A composition comprised of a sulfonated polyaniline composition of formula I for use as a chemical sensor, wherein through exposure to a reactive chemical the color and/or conductivity of the sulfonated polyaniline composition is changed.

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17. A composition for conducting electricity, wherein the electrical conductivity is in the range of about 0.5 S/cm wherein the composition comprises
5 a sulfonated polyaniline composition of the formula I.

18. The composition as claimed in claim 17, wherein the composition is used as discharge layers for an electron beam lithography process.

10 19. The composition as claimed in claim 17, wherein the composition is used as a medium for electrostatic discharge.

20. The composition as claimed in claim 18, wherein the composition is blended, entrained in a matrix of, or copolymerized with an insulating polymer to
15 form a conducting polymer.

21. The composition as claimed in claim 20, wherein the conducting polymer is used with bulk coverings including carpets and fabrics.

20 22. The composition as claimed in claim 20, wherein the conducting polymer is used in conductive seals, joints, or moldings.

23. A method for conducting electricity comprising exposing a sulfonated polyaniline composition of the formula I to a constant current source, whereby
25 electricity is conducted by the sulfonated polyaniline composition.

24. A composition for absorbing electromagnetic radiation, wherein the electromagnetic radiation possesses a wavelength generally in the range of from about 1000 Angstroms to about 50 meters, wherein the composition comprises a
30 sulfonated polyaniline composition of the formula I.

25. The composition as claimed in claim 24, wherein the electromagnetic radiation is microwave radiation which possesses a wavelength generally in the range of from about 0.04cm to about 25cm.

35

26. The composition as claimed in claim 24, wherein the electromagnetic radiation is infrared radiation which possesses a wavelength generally in the range of from about 3,000 Angstroms to about 0.04cm.

27. The composition as claimed in claim 24, wherein the electromagnetic radiation is visible light radiation which possesses a wavelength generally in the range of from about 4,000 Angstroms to about 8,000 Angstroms.

5

28. The composition as claimed in claim 24, wherein the electromagnetic radiation is ultraviolet radiation which possesses a wavelength generally in the range of from about 100 Angstroms to about 4,000 Angstroms.

10

29. A method of absorbing electromagnetic radiation comprising exposing a sulfonated polyaniline composition of the formula I to electromagnetic radiation, whereby the electromagnetic radiation is absorbed by the sulfonated polyaniline composition.

15

30. The method of absorbing electromagnetic radiation as claimed in claim 29 comprising exposing the sulfonated polyaniline composition to infrared radiation, whereby the infrared radiation is absorbed by the sulfonated polyaniline composition.

20

31. The method of absorbing electromagnetic radiation as claimed in claim 29 comprising exposing the sulfonated polyaniline composition to visible light radiation, whereby the visible light radiation is absorbed by the sulfonated polyaniline composition.

25

32. The method of absorbing electromagnetic radiation as claimed in claim 29 comprising exposing the sulfonated polyaniline composition to ultraviolet radiation, whereby the ultraviolet radiation is absorbed by the sulfonated polyaniline composition.

30

33. The method of absorbing electromagnetic radiation as claimed in claim 29 comprising exposing the sulfonated polyaniline composition to microwave radiation, whereby the microwave radiation is absorbed by the sulfonated polyaniline composition.

35

34. A method of applying heat to a substrate comprising:
(a) applying to a substrate an electromagnetic radiation-absorbing sulfonated polyaniline composition, or a partially self-protonated salt thereof; and,

(b) exposing the electromagnetic radiation-absorbing sulfonated polyaniline composition, or the partially self-protonated salt thereof, to electromagnetic radiation, whereby the electromagnetic radiation-absorbing sulfonated polyaniline composition, or the partially self-protonated salt thereof
5 absorbs the electromagnetic radiation.

35. The method as claimed in claim 34 whereby heat is generated by the absorption of the electromagnetic radiation and the heat is transferred from the sulfonated polyaniline composition or the partially self-protonated salt thereof
10 to the substrate.

36. The method as claimed in claim 34, wherein the electromagnetic radiation is microwave radiation.

15

37. The method as claimed in claim 34, wherein the electromagnetic radiation is infrared radiation.

38. The method as claimed in claim 34, wherein the electromagnetic
20 radiation is visible radiation.

39. The method as claimed in claim 34, wherein the electromagnetic radiation is ultraviolet radiation.

40. The method as claimed in claim 34, wherein the electromagnetic
25 radiation-absorbing sulfonated polyaniline composition is of the general formula I.

41. The method as claimed in claim 34, wherein the electromagnetic
30 radiation-absorbing sulfonated polyaniline composition is of molecular weight in the range of from approximately 300 (oligomers of polyaniline) to in excess of 100,000.

42. The method as claimed in claim 34, wherein the electromagnetic
35 radiation-absorbing sulfonated polyaniline composition is applied to the substrate by a method selected from the group consisting of spray coating, dip coating, spin casting, melt extrusion, transfer roll coating, and brush-on coating.

43. The method as claimed in claim 34 wherein the substrate is a material selected from the group consisting of synthetic fibrous material, natural fibrous material, inorganic filler material, organic polymeric material, woven fabric material, non-woven fabric material, and silicate-containing material.

44. A method of adhering two or more materials comprising:

(a) applying to at least one of the materials a microwave radiation-absorbing sulfonated polyaniline composition, or a partially self-protonated salt thereof;

(b) contacting the materials to be adhered such that the microwave radiation-absorbing sulfonated polyaniline composition, or the partially self-protonated salt thereof, is contacting both materials to be adhered; and,

(c) exposing the microwave radiation-absorbing sulfonated polyaniline composition, or the partially self-protonated salt thereof, to microwave radiation sufficient to cause the materials to adhere to each other.

45. The method as claimed in claim 44, wherein one of the materials to be adhered is a higher temperature melting microwave transmissive material and another material to be adhered is a lower temperature melting material, whereby the material is caused to melt.

46. The method as claimed in claim 44, wherein at least one of the materials to be adhered is a plastic.

47. The method as claimed in claim 44, wherein at least one of the materials to be adhered comprises a silicate-containing material.

48. A method of changing the refractive index of sulfonated polyaniline comprising:

(a) applying sulfonated polyaniline to a phototransmissive substrate;

(b) applying a first beam of light of wavelength x at a critical angle y to the sulfonated polyaniline; and

(c) applying a second beam of light of wavelength z to the sulfonated polyaniline, whereby the second beam is absorbed by the sulfonated polyaniline changing the index of refraction of the sulfonated polyaniline, whereby the transmission of the first beam through the phototransmissive substrate is altered

49. A method of changing the refractive index of a sulfonated polyaniline composition comprising:

- (a) applying a first beam of light of wavelength x at a critical
5 angle y to the sulfonated polyaniline; and
- (b) applying a second beam of light of wavelength z to the sulfonated polyaniline, whereby the second beam is absorbed by the sulfonated polyaniline changing the index of refraction of the sulfonated polyaniline, whereby the transmission of the first beam through the sulfonated polyaniline
10 composition is altered.

50. A method for absorbing electromagnetic waves comprising exposing a sulfonated polyaniline polymeric composition or a partially self-protonated salt thereof to radar waves whereby the sulfonated polyaniline composition or the
15 salt thereof absorbs the radar waves.

51. A method for reducing the detectability by radar of an object comprising applying to the object a sulfonated polyaniline composition or a partially self-protonated salt thereof in an amount sufficient to absorb at least
20 some radar radiation to which the object may be exposed, thereby reducing the detectability by radar of the object.

52. A method of coupling an optical signal from one phototransmissive substrate to another phototransmissive substrate by means of sulfonated
25 polyaniline composition comprising:

- (a) applying a sulfonated polyaniline composition between a first and a second phototransmissive substrate, whereby the sulfonated polyaniline is in contact with both phototransmissive substrates;
- (b) inducing an optical signal through the first phototransmissive
30 substrate; and,
- (c) exposing the sulfonated polyaniline composition to light of sufficient intensity and wavelength to alter the index of refraction of the sulfonated polyaniline composition such that the optical signal induced through the first phototransmissive substrate is coupled through the sulfonated
35 polyaniline composition into the second phototransmissive substrate, whereby the optical signal is transmitted through the second phototransmissive substrate.

53. A method of providing electronic shielding comprising providing a layer of a sulfonated polyaniline composition on the object to be shielded, whereby the entrance and egress of electromagnetic radiation is prevented.

5

54. A method of producing a thermal switch comprising:

(a) contacting a microwave radiation-absorbing sulfonated polyaniline composition, or a partially self-protonated salt thereof with a thermocouple; and,

10 (b) exposing the microwave radiation-absorbing sulfonated polyaniline composition, or the partially self-protonated salt thereof, to microwave radiation sufficient to cause the composition to absorb enough microwave radiation to generate heat, whereby the thermocouple is activated.

15 55. A method for masking a radiation curable polymer applied to an electronic circuit or device comprising:

(a) applying a radiation-curable polymer or prepolymer to an electronic device or circuit;

(b) applying to the radiation-curable polymer or prepolymer a
20 sulfonated polyaniline composition;

(c) exposing the device or circuit with the curable polymer or prepolymer and the sulfonated polyaniline composition to radiation sufficient to cure the curable polymer or prepolymer, whereby the sulfonated polyaniline composition absorbs some of the ultraviolet radiation; and,

25 (d) removing the sulfonated polyaniline and any uncured curable polymer or prepolymer.

56. A method of producing an electromagnetic radiation absorbing cloth comprising:

30 (a) extruding a polymeric material comprising a sulfonated polyaniline composition;

(b) creating a fiber from the extruded polymeric material; and,

(c) preparing a cloth comprising fiber created from the extruded polymeric material whereby the sulfonated polyaniline composition of the cloth
35 absorbs electromagnetic radiation.

57. The method as claimed in claim 56 wherein the polymeric material comprising a sulfonated polyaniline composition further comprises an organic

material selected from the group consisting of polyethylene, polyester, polyimide, nylon, cellulose nitrate, cellulose acetate, and polyvinyl chloride.

5 58. An electromagnetic radiation absorbing cloth produced by the method of claim 56.

59. An article produced from the electromagnetic radiation absorbing cloth of claim 58.

10

60. A light valve for modulating the light coupled from one light transmitting medium to an adjacent light transmitting medium, the light valve comprising:

(a) a mass of electromagnetic radiation absorbing sulfonated
15 polyaniline forming one of the light transmitting media;

(b) a modulating light source for radiating light at a controllable intensity upon at least a portion of the sulfonated polyaniline mass for controlling its index of refraction;

(c) a modulated light source for radiating light through a first one
20 of the light transmitting media adjacent the interface between the media; and,

(d) means for controllably varying the intensity of light incident upon the sulfonated polyaniline mass from the modulating light source to thereby modulate light coupled from the first medium to the other.

25 61. The light valve in accordance with claim 60, wherein one of said media is a solid light conductor having a layer of the sulfonated polyaniline upon a surface of the conductor.

62. The light valve in accordance with claim 61, wherein the light
30 conductor is an optical fiber with the sulfonated polyaniline on its longitudinal surface.

63. The light valve in accordance with claim 61, wherein the light conductor is an optical fiber with the sulfonated polyaniline on an endface.

35

64. The light valve in accordance with claim 63, wherein the endface is lapped at an angle to the optical axis of the fiber which is substantially the critical angle for the sulfonated polyaniline/conductor interface.

65. The light valve in accordance with claim 60 further comprising a third medium in the form of a light conductor and wherein the first medium is a first light conductor and the sulfonated polyaniline mass is interposed between
5 the two light conductors for coupling light from the first conductor to the sulfonated polyaniline and from the sulfonated polyaniline to the second conductor.

66. The light valve in accordance with claims 60, 61, 62, 63, 64 or 65,
10 wherein the sulfonated polyaniline mass is a layer upon a light conductor which together form the two media, and the modulated light source is positioned to direct light at a selected frequency range from within one medium upon the media interface at an angle of incidence which is substantially greater than the critical angle for that interface when the modulating light is at a minimum
15 intensity, wherein the light coupled to the other medium is increased as the intensity of the modulating light is increased to increase the critical angle of the interface to an angle greater than said angle of incidence.

67. The light valve in accordance with claims 60, 61, 62, 63, 64 or 65,
20 wherein the sulfonated polyaniline mass is a layer upon a light conductor which together form the two media, and the modulated light source is positioned to direct light at a selected frequency range from within one medium upon the media interface at an angle of incidence which is substantially less than the critical angle for that interface when the modulating light is at a minimum
25 intensity, wherein the light coupled to the other medium is decreased as the intensity of the modulating light is increased to decrease the critical angle of the interface to an angle less than said angle of incidence.

68. An apparatus for controllably varying the phase velocity of
30 propagating light, the apparatus comprising:

- (a) a light conductor through which the light propagates;
- (b) a layer of electromagnetic radiation absorbing sulfonated polyaniline upon a surface of the conductor;
- (c) a variable intensity modulating light source positioned to
35 radiate light upon the sulfonated polyaniline layer; and,
- (d) means for controllably varying the intensity of the modulating light source.

69. A microwave attenuator comprising a mass of electromagnetic radiation absorbing emeraldine salt form of sulfonated polyaniline positioned in the propagation path of the microwave.

5

70. The attenuator in accordance with claim 69, wherein the sulfonated polyaniline mass has a variation in its self-protonation as a function of distance along the axis of microwave propagation.

10

71. The attenuator in accordance with claim 70, wherein the self-protonation varies from a minimum at a microwave input end of the propagation axis along the sulfonated polyaniline mass to a maximum at an opposite, output end along the propagation axis.

15

72. The attenuator in accordance with claim 71, wherein the average gradient of the variation in self-protonation is approximately a linear function of distance along the propagation axis.

20

73. The attenuator in accordance with claim 71, wherein the attenuator is formed of a plurality of laminated layers of the sulfonated polyaniline, each layer having a differing self-protonation level.

25

74. The attenuator in accordance with claims 69, 70, 71, 72 or 73, wherein the sulfonated polyaniline mass is one electrode of an electrochemical cell having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass to vary its self-protonation and thereby vary its attenuation.

30

75. The attenuator in accordance with claim 74, wherein the sulfonated polyaniline mass comprises a series of discrete segments arranged along the axis of propagation and wherein each segment forms an electrode of a different electrochemical cell each having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass of each segment to vary its self-protonation and thereby its attenuation across the entire mass of segments.

35

76. The attenuator in accordance with claims 69, 70, 71, 72 or 73, wherein the mass is a layer upon at least one interior wall of a wave guide.

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77. The attenuator in accordance with claim 76, wherein the sulfonated polyaniline mass is one electrode of an electrochemical cell having a second electrode and an interposed electrolyte and wherein there is further provided
5 means for controllably varying the potential of the sulfonated polyaniline mass to vary its self-protonation and thereby vary its attenuation.

78. The attenuator in accordance with claim 77, wherein the sulfonated polyaniline mass comprises a series of discrete segments arranged along the axis
10 of propagation and wherein each segment forms an electrode of a different electrochemical cell each having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass of each segment to vary its self-protonation and thereby its attenuation for controlling the self-protonation
15 gradient across the entire mass of segments.

79. The attenuator in accordance with claims 69, 70, 71, 72 or 73, wherein the mass is within a waveguide and spans between walls of the waveguide and extends a selected distance along its propagation axis.

20

80. The attenuator in accordance with claim 79, wherein the sulfonated polyaniline mass is one electrode of an electrochemical cell having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass
25 to vary its self-protonation and thereby vary its attenuation.

81. The attenuator in accordance with claim 80, wherein the sulfonated polyaniline mass comprises a series of discrete segments arranged along the axis of propagation and wherein each segment forms an electrode of a different
30 electrochemical cell each having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass of each segment to vary its self-protonation and thereby its attenuation of radiation.

82. The attenuator in accordance with claim 79, wherein the sulfonated polyaniline mass has a progressively greater cross-sectional area in planes perpendicular to the axis of propagation extending from a minimum area at its microwave input end to a maximum area at its opposite end along the propagation axis.

35

83. The attenuator in accordance with claims 69, 70, 71, 72 or 73, wherein the sulfonated polyaniline mass is a layer bonded to the exterior surface of a microwave strip conductor.

5

84. The attenuator in accordance with claim 83, wherein the sulfonated polyaniline mass is one electrode of an electrochemical cell having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass to vary its self-protonation and thereby vary its attenuation.

10

85. The attenuator in accordance with claim 84, wherein the sulfonated polyaniline mass comprises a series of discrete segments arranged along the axis of propagation and wherein each segment forms an electrode of a different electrochemical cell each having a second electrode and an interposed electrolyte and wherein there is further provided means for controllably varying the potential of the sulfonated polyaniline mass of each segment to vary its self-protonation and thereby its attenuation of radiation.

15

86. The attenuator in accordance with claim 69, wherein the sulfonated polyaniline mass is a layer which is bonded to an exterior surface of a microwave strip conductor and has a variation in its self-protonation as a function of distance along the axis of propagation which varies from a minimum at a microwave input end to a region of maximum self-protonation and then varies from the maximum self-protonation to a minimum self-protonation at an opposite end along the propagation axis to form an attenuator with minimized reflections.

20

25

87. A method for shielding from electromagnetic waves comprising interposing a layer of a sulfonated polyaniline salt between a source of the waves and an object to be shielded.

30

88. The method in accordance with claim 87, wherein the layer of sulfonated polyaniline is simultaneously also connected in an electrical circuit to conduct current.

35

89. The method in accordance with claim 88, wherein the layer is positioned around electrical conductors to provide a shielded cable and the layer also is connected to ground a device connected to the cable

90. A thermally responsive film heatable by microwave energy and comprising a thermally responsive film having a microwave radiation absorbing self-protonated sulfonated polyaniline salt distributed in the thermally responsive film.

91. The film in accordance with claim 90, wherein the film is a thermally activated shrink wrap film.

10 92. A method for providing a barrier to fluid passage and for removing that barrier comprising:

(a) distributing a microwave radiation absorbing self-protonated, emeraldine salt of sulfonated polyaniline in a thermally deformable film;

(b) forming a barrier with said film; and,

15 (c) irradiating the film with microwave energy.

93. A method for applying a film tightly around at least a portion of an object comprising:

20 (a) distributing a microwave radiation absorbing, self-protonated, emeraldine salt of sulfonated polyaniline in a thermally activated shrink wrap film;

(b) loosely surrounding the object with the film; and,

(c) irradiating the film with microwave energy.

25 94. An erasable optical information storage apparatus comprising:

(a) a rotating optical disk composed of a sulfonated polyaniline;

(b) a writing laser and mirror combination for writing bits of information;

30 (c) a reading laser and mirror combination for reading photoinduced information;

(d) an erasing laser and mirror combination for the bit-wise erasure of information; and,

(e) a detector for outputting the information stored.

35 95. A method for the storage and retrieval of information in an optical high density erasable format comprising:

(a) maintaining a storage unit composed in part of a film of a sulfonated polyaniline at a temperature at or below 100 Kelvin;

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(b) exposing the storage unit to a writing beam representative of the information or data, the writing beam having a known photon frequency and intensity to modify the optical absorption characteristics of the sulfonated polyaniline film; and,

(c) exposing the storage unit to a reading beam having a second known photon frequency and intensity, the second known frequency and intensity being predetermined to match the altered optical absorption spectrum of the film, whereby the information or data is retrieved from the altered optical absorption spectrum.

96. The method of claim 95 further including the step of erasing the data stored by the writing beam input by elevating the temperature of the storage unit to room temperature.

97. The method of claim 95 further including the step of erasing the data stored by the writing beam input by selected bits by temporarily elevating the temperature of the selected bit of the storage unit to room temperature.

98. The method of claim 95 further including the step of erasing the data stored by the writing beam input by exposing the storage unit to an intense light source of selected wavelength.

99. The method of claim 95 further including the step of erasing the data stored by the writing beam input by selected bits by exposure of the selected bits of the storage unit to an intense directed light beam of selected wavelength.

100. The method of claim 95 further including the step of stacking the information or data stored by the writing beam by selectively altering the intensity of the writing beam, wherein the intensity of the modification of the optical absorption characteristics of the sulfonated polyaniline film is directly responsive to the intensity of the writing beam, thereby enabling more than one bit of information to be written at a selected site on the storage unit.

101. A method for producing a three dimensional holographic grating comprising:

(a) dispersing a thick specimen of a film of a sulfonated polyaniline in a transparent host polymer such as kapton or polycarbonate;

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(b) focusing two light beams at the sulfonated polyaniline film to create an interference pattern between the focused light beams with the sulfonated polyaniline film; and,

5 (c) exposing the sulfonated polyaniline film to a reading beam.

102. A method for the storage and retrieval of data or information in an optical high density erasable format comprising:

(a) providing a storage unit composed in part of a film of a
10 polyorthotoluidine and naphthal version of an emeraldine form of sulfonated polyaniline;

(b) exposing the storage unit to a writing beam representative of the information or data, the writing beam having a known photon frequency and intensity to modify the optical absorption characteristics of the sulfonated
15 polyaniline film; and,

(c) exposing the storage unit to a reading beam having a second known photon frequency and intensity, the known frequency and intensity being predetermined to match the altered optical absorption spectrum of the sulfonated polyaniline film whereby the information or data is retrieved from the
20 altered optical absorption spectrum.

103. The method of claim 102 further including the step of erasing the data stored by the writing beam input by exposing the storage unit to a temperature elevated distinctly above room temperature.

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104. A method for the storage and retrieval of data or information in an optical high density erasable format comprising:

(a) providing a storage unit composed in part of a film of sulfonated polyaniline or derivatized sulfonated polyaniline composed of the
30 formula I;

(b) exposing the storage unit to a writing beam representative of the information or data, the writing beam having a known photon frequency and intensity to modify the optical absorption characteristics of the sulfonated polyaniline film; and,

35 (c) exposing the storage unit to a reading beam having a second known photon frequency and intensity, the second known frequency and intensity being predetermined to match the altered optical absorption spectrum of the film whereby the information or data is retrieved from the altered optical absorption spectrum.

105. The method of claim 104 further including the step of erasing the data stored by the writing beam input by exposing the storage unit to a temperature elevated distinctly above room temperature.

5

106. The method of claim 105, wherein $R_1 = \text{SO}_3\text{H}$, $R_2 = R_3 = R_4 = R_5 = R_6 = \text{H}$ and $y = 0.5$ and $x = 0.2 \sim 1$ and maintaining such storage unit at a temperature not exceeding 200K.

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107. The method of claim 106 further including the step of erasing the data stored by the writing beam input by exposing the storage unit to a temperature elevated distinctly above 200K.

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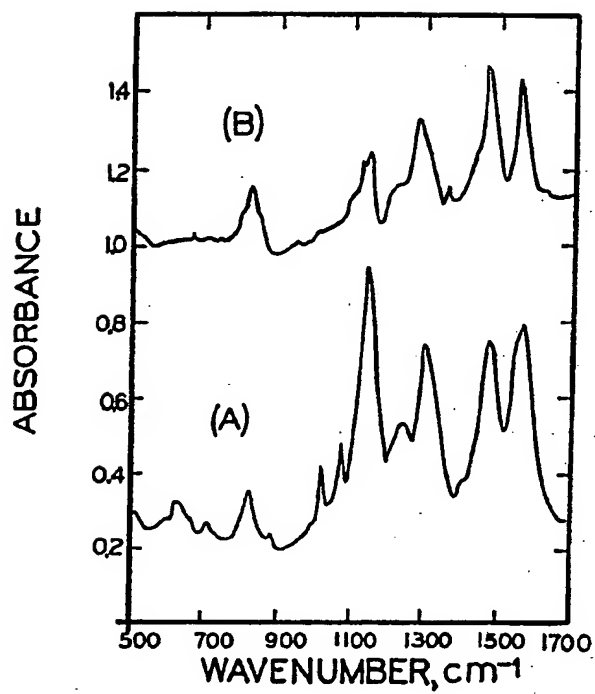


FIG. 1

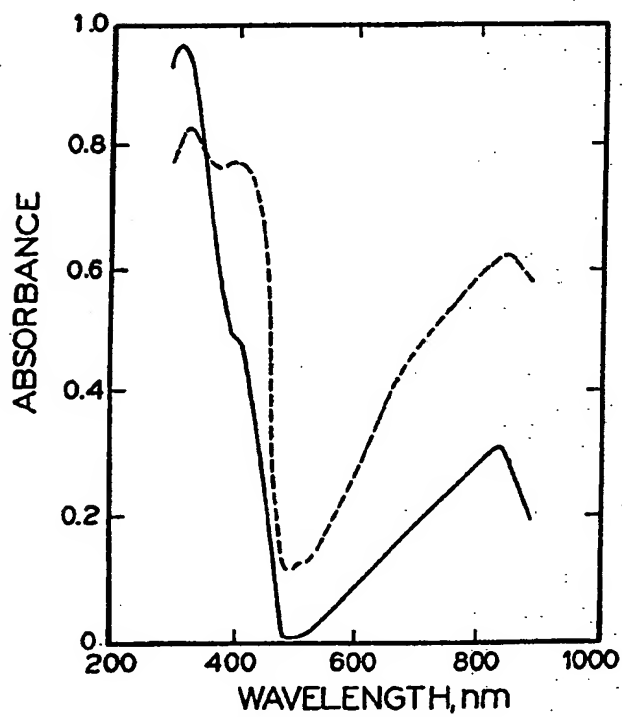


FIG. 2

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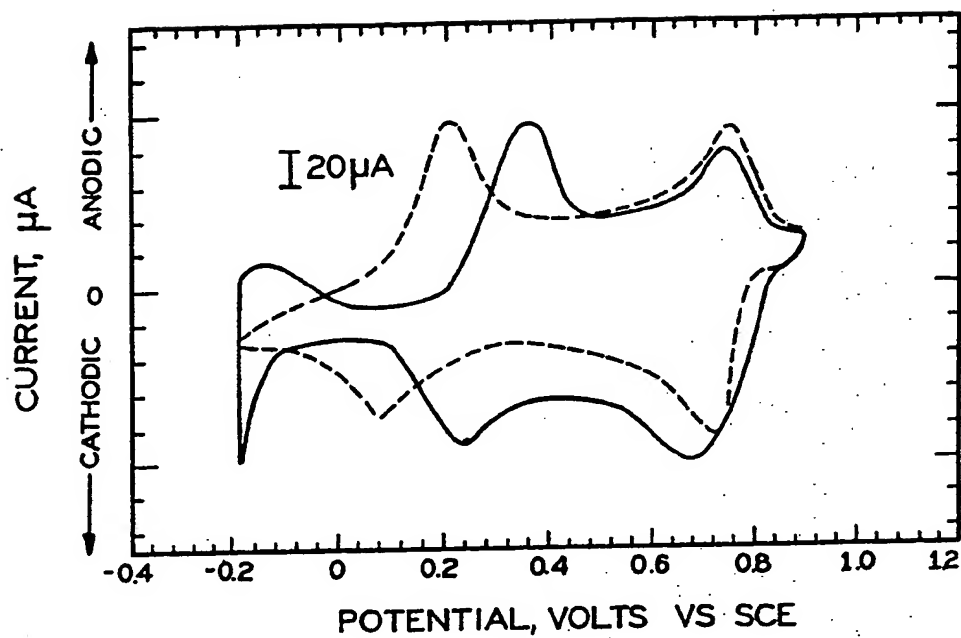


FIG. 3

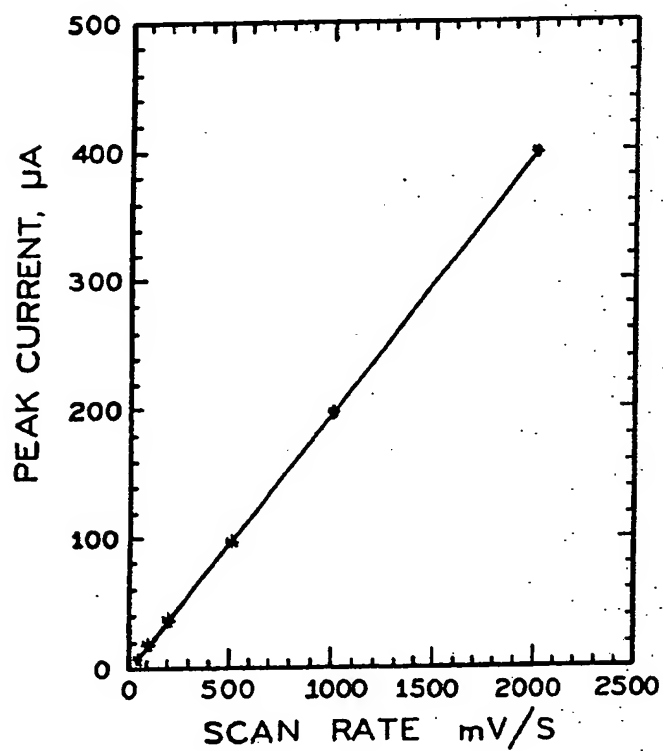
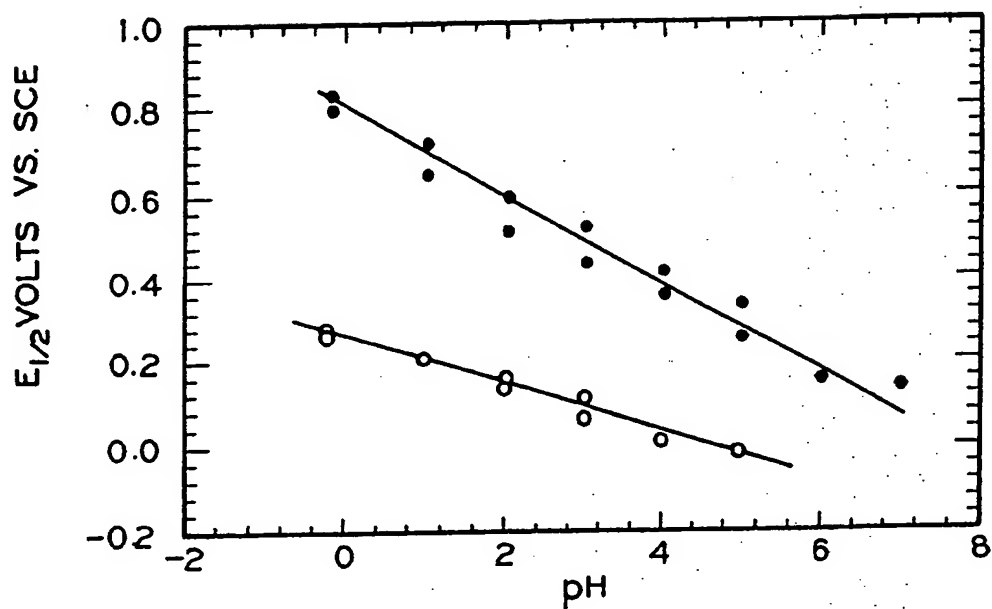
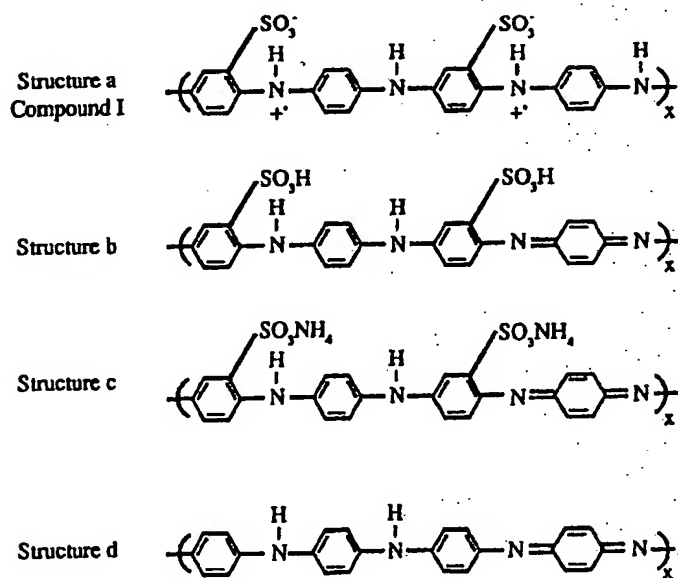


FIG. 4

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—FIG. 5



—FIG. 6

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FIG. 7

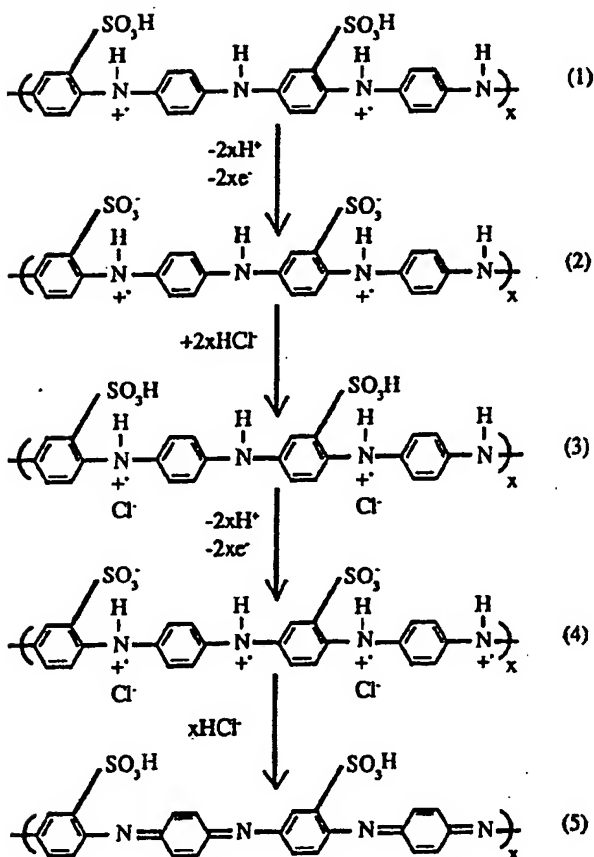
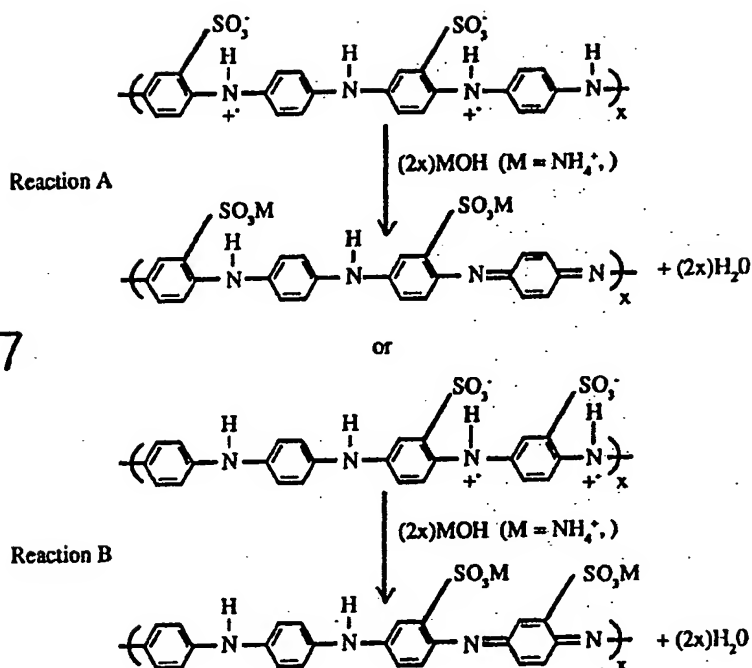


FIG. 8

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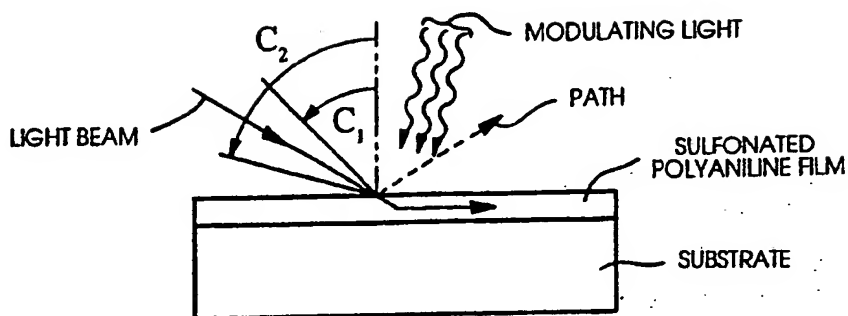


FIG. 9

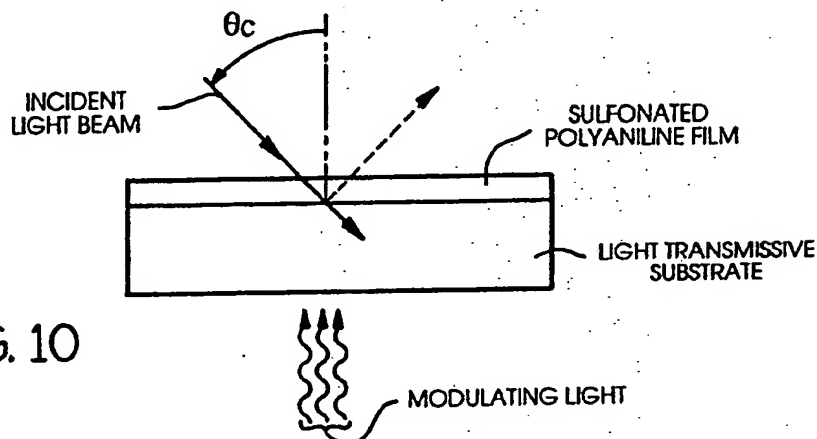


FIG. 10

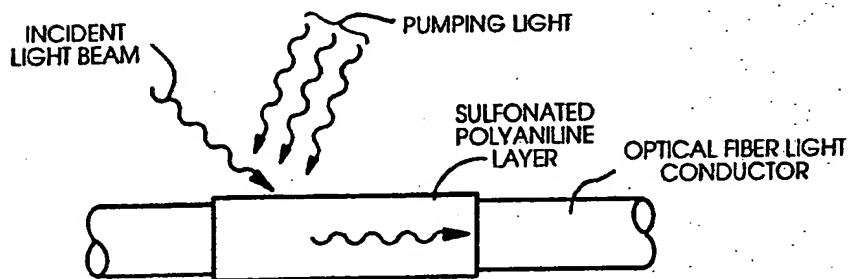


FIG. 11

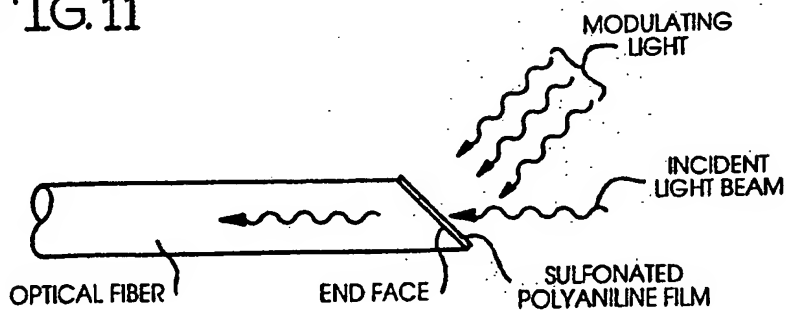


FIG. 12

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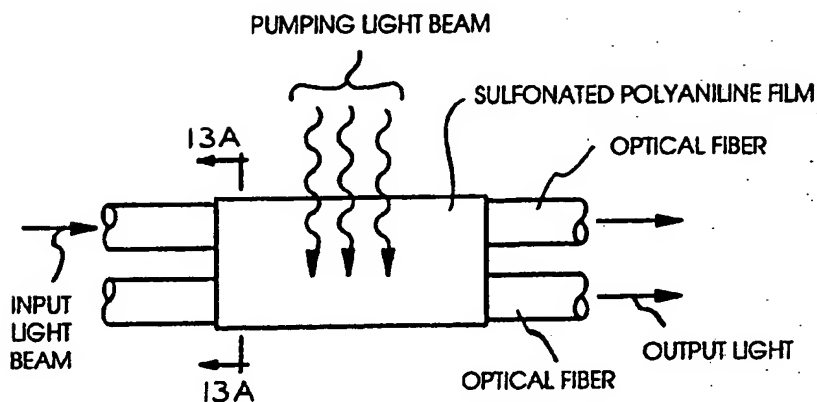


FIG. 13



FIG. 14

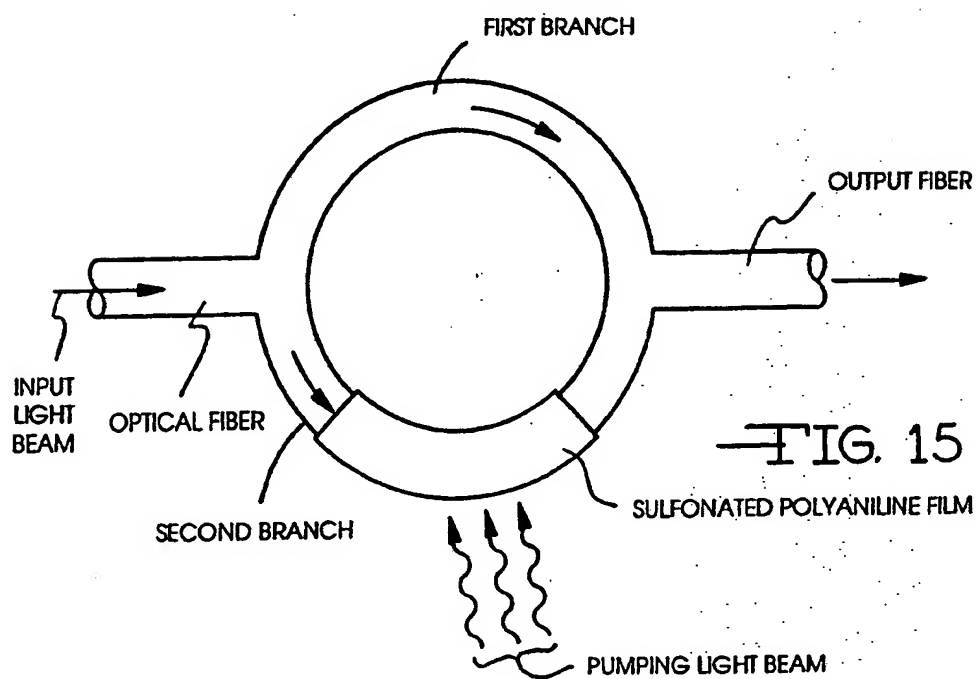


FIG. 15

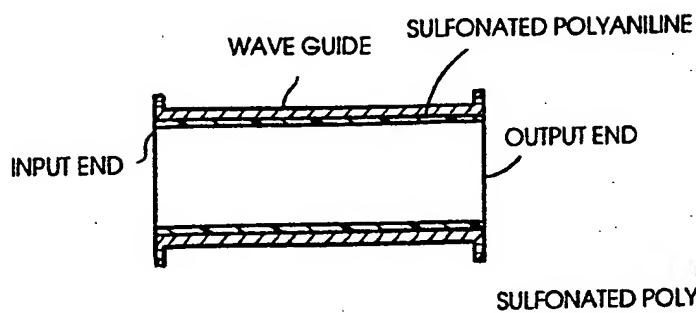


FIG. 16

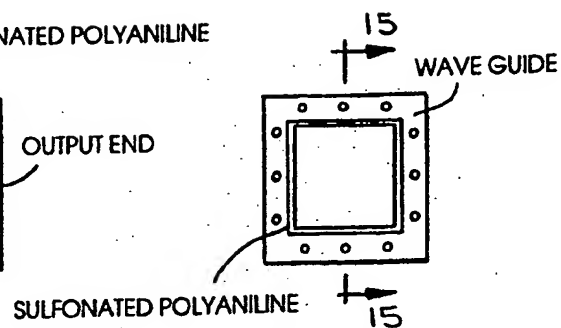


FIG. 17

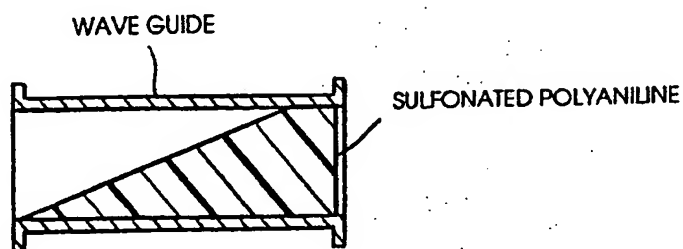


FIG. 18

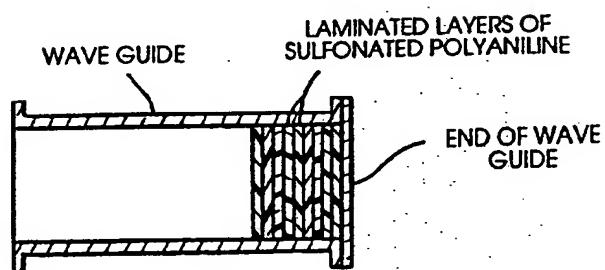


FIG. 19

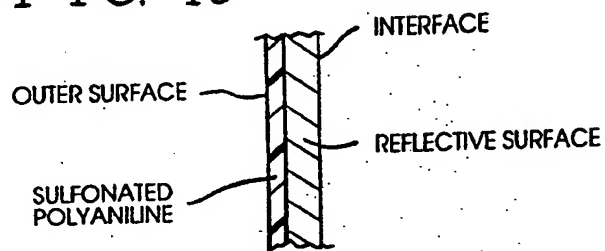


FIG. 20

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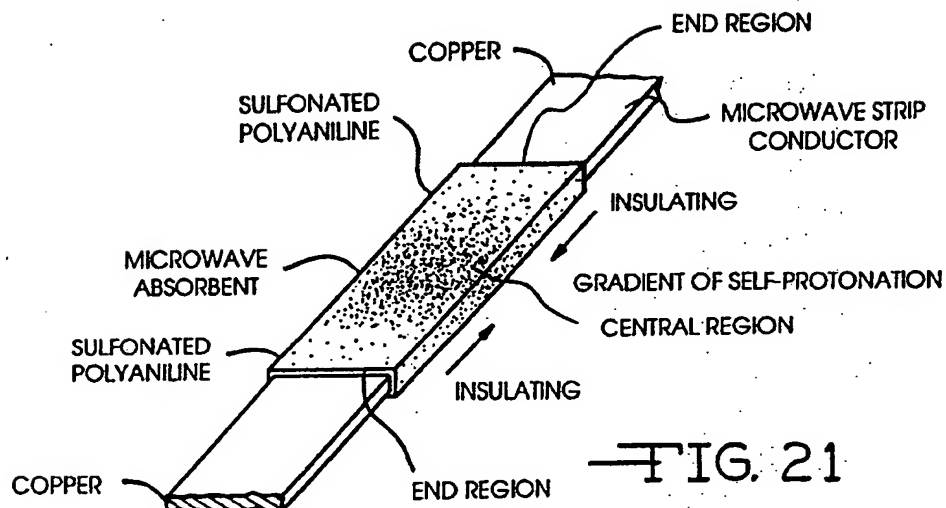


FIG. 21

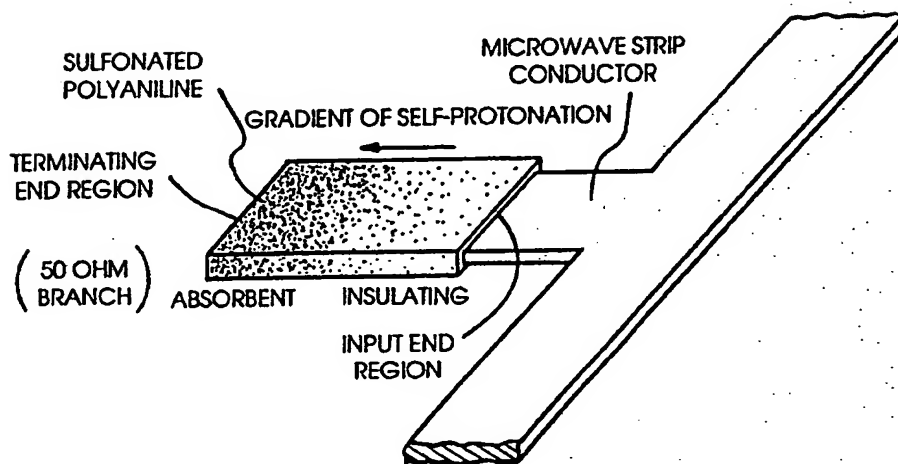


FIG. 22

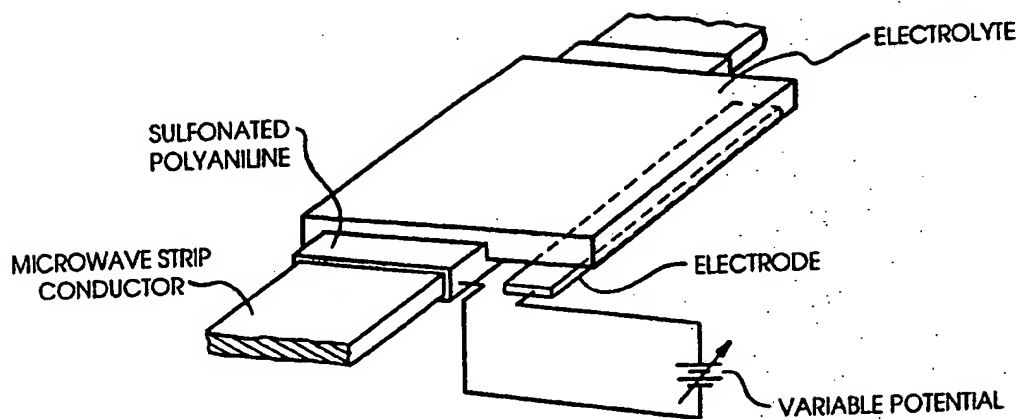


FIG. 23

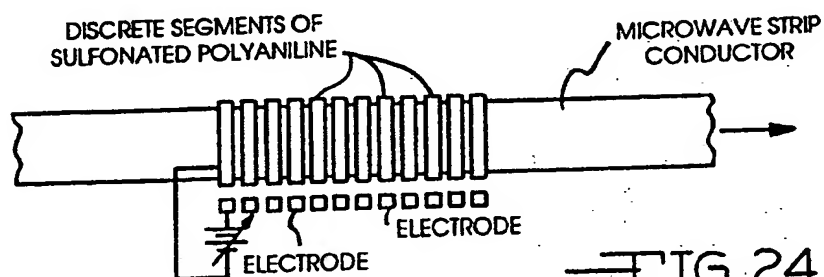


FIG. 24

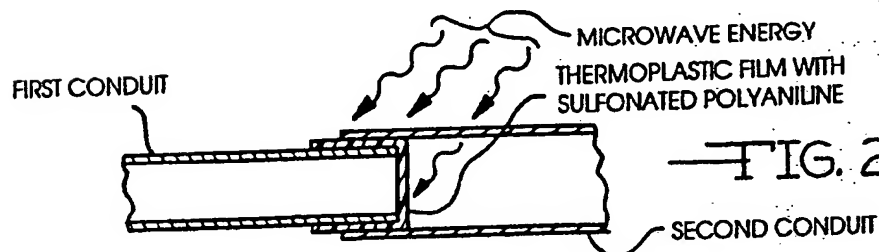


FIG. 25

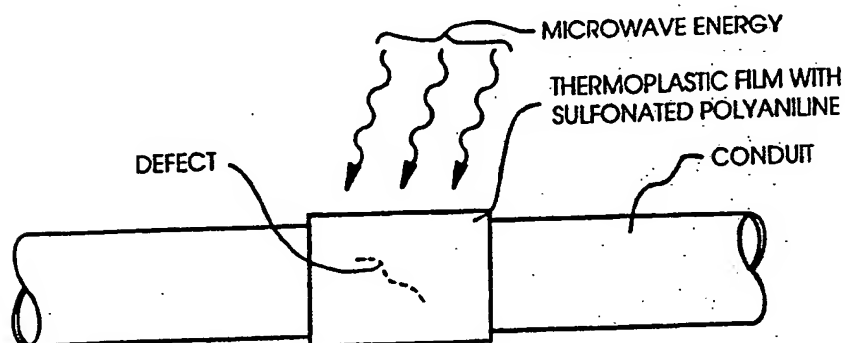
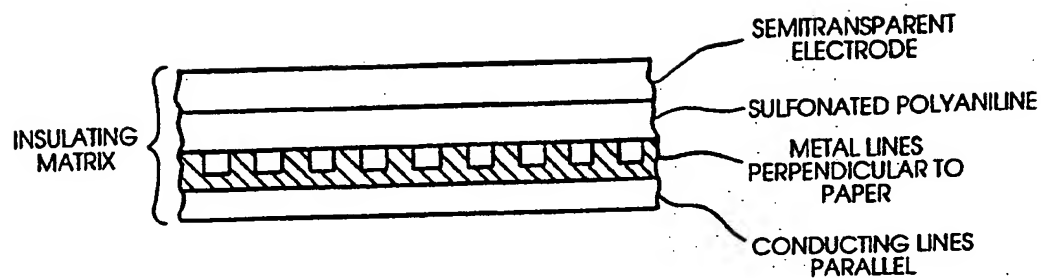
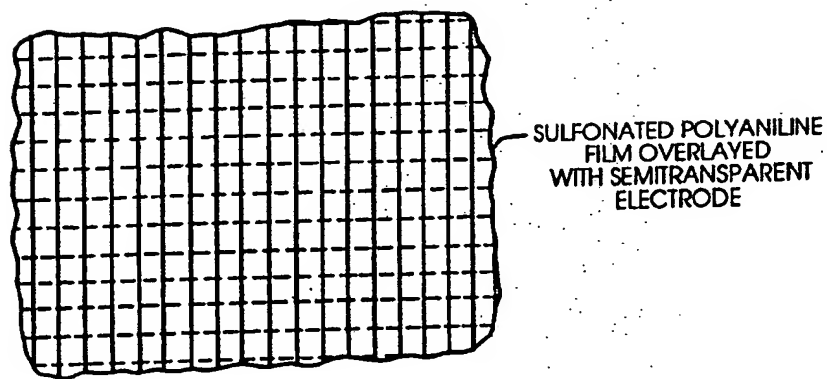


FIG. 26

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—FIG. 27



—FIG. 28

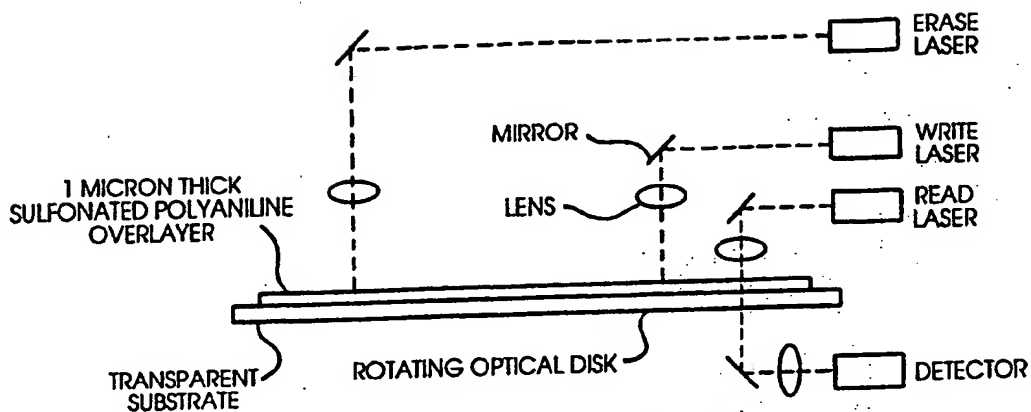


FIG. 29

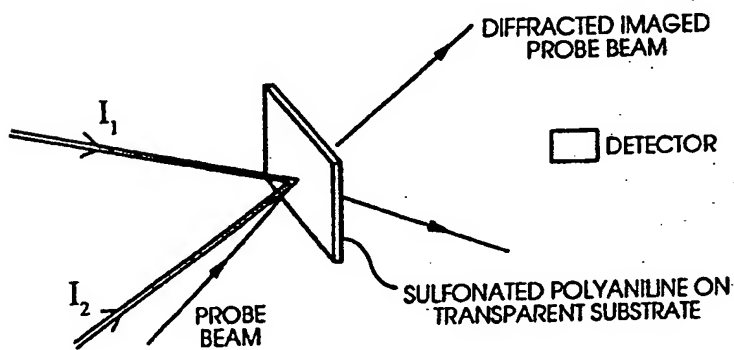


FIG. 30

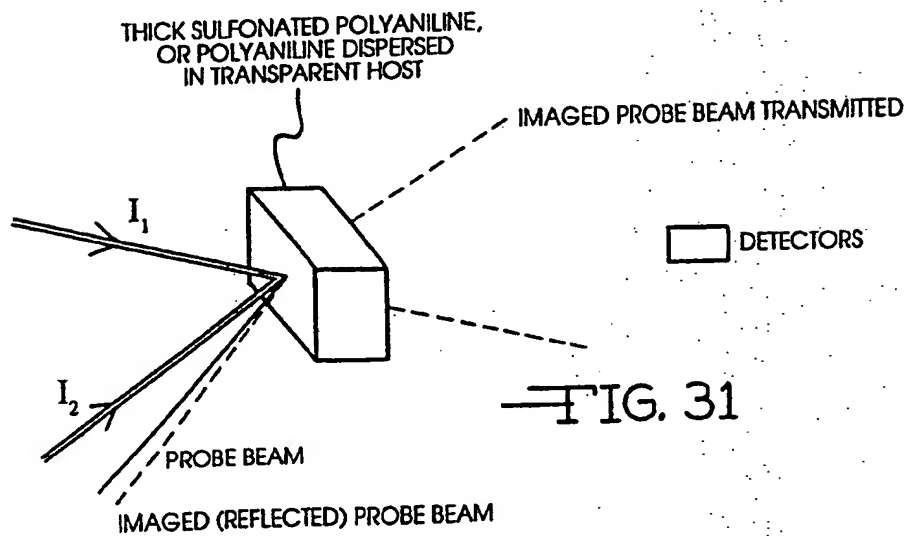


FIG. 31

INTERNATIONAL SEARCH REPORT

International Application No. PCT/US90/05900

I. CLASSIFICATION OF SUBJECT MATTER (if several classification symbols apply, indicate all) ⁶		
According to International Patent Classification (IPC) or to both National Classification and IPC		
IPC (5): F28F 13/00; C25D 5/02, 5/54; C25B 3/02; (cont.) U.S. CL. 427/123; 165/96, 185; 204/15, 20, 59R, 72, (cont.)		
II. FIELDS SEARCHED		
Minimum Documentation Searched ⁷		
Classification System	Classification Symbols	
U.S.	165/96, 185; 204/15, 20, 59R, 72, 78; 252/500, 518; 350/357, 363; 427/123; 428/195, 212; 525/540; 528/319, 422, 487, 490	
Documentation Searched other than Minimum Documentation to the extent that such documents are included in the fields searched ⁸		
III. DOCUMENTS CONSIDERED TO BE RELEVANT ⁹		
Category [*]	Citation of Document, ¹¹ with indication, where appropriate, of the relevant passages ¹²	Relevant to Claim No. ¹³
X	US, A, 4,586,792 (YANG) 06 May 1986 See abstract and columns 1-8 et seq.	1-9, 11-15
Y	US, A, 4,742,867 (WALSH) 10 May 1988 See abstract and columns 1-4 et seq.	4-9, 11-15
X	US, A, 4,822,638 (YANIGER) 18 April 1989 See abstract and columns 1-10 et seq.	1-9, 11-15
X	JP, A, 61-197633 (TAMURA) 01 September 1986; See translated copy pages 1-20.	1-9
Y	JOURNAL OF APPLIED POLYMER SCIENCE, Vol. 20 issued 1976, A. NOSHAY, "Sulfonated Polysulones", see pages 1885-1903.	1-9
Y	JOURNAL VAC. SCI. TECHNOL., B7(6), issued 1989 November/December, Manic Angelopoulos, "Conducting Polyanilines: Discharge layers for electron-beam lithography", See pages 1519-1523	1-9, 11-15
<p>[*] Special categories of cited documents: ¹⁰</p> <p>"A" document defining the general state of the art which is not considered to be of particular relevance</p> <p>"E" earlier document but published on or after the international filing date</p> <p>"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)</p> <p>"O" document referring to an oral disclosure, use, exhibition or other means</p> <p>"P" document published prior to the international filing date but later than the priority date claimed</p> <p>"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention</p> <p>"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step</p> <p>"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.</p> <p>"&" document member of the same patent family</p>		
IV. CERTIFICATION		
Date of the Actual Completion of the International Search	Date of Mailing of this International Search Report	
04 FEBRUARY 1991	13 MAR 1991	
International Searching Authority	Signature of Authorizing Officer	
ISA/US	Patricia Hampton-Hightower	

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